

Features

- ◆ 512K x 36, 1M x 18 memory configurations
- ◆ Supports high performance system speed - 100 MHz (7.5 ns Clock-to-Data Access)
- ◆ ZBT™ Feature - No dead cycles between write and read cycles
- ◆ Internally synchronized output buffer enable eliminates the need to control \overline{OE}
- ◆ Single R/W (READ/WRITE) control pin
- ◆ 4-word burst capability (Interleaved or linear)
- ◆ Individual byte write (BW1 - BW4) control (May tie active)
- ◆ Three chip enables for simple depth expansion
- ◆ 2.5V power supply ($\pm 5\%$)
- ◆ 2.5V ($\pm 5\%$) I/O Supply (VDDO)
- ◆ Power down controlled by ZZ input
- ◆ Boundary Scan JTAG Interface (IEEE 1149.1 Compliant)
- ◆ Packaged in a JEDEC standard 100-pin plastic thin quad flatpack (TQFP), 119 ball grid array (BGA)

Description

The IDT71T75702/902 are 2.5V high-speed 18,874,368-bit (18 Megabit) synchronous SRAMs organized as 512K x 36 / 1M x 18. They are designed to eliminate dead bus cycles when turning the bus around between reads and writes, or writes and reads. Thus they have been given the name ZBT™, or Zero Bus Turnaround.

Address and control signals are applied to the SRAM during one clock cycle, and on the next clock cycle the associated data cycle occurs, be it read or write.

The IDT71T75702/902 contain address, data-in and control signal registers. The outputs are flow-through (no output data register). Output enable is the only asynchronous signal and can be used to disable the outputs at any given time.

A Clock Enable (\overline{CEN}) pin allows operation of the IDT71T75702/902 to be suspended as long as necessary. All synchronous inputs are ignored when \overline{CEN} is high and the internal device registers will hold their previous values.

There are three chip enable pins ($\overline{CE1}$, $\overline{CE2}$, $\overline{CE3}$) that allow the user to deselect the device when desired. If any one of these three is not asserted when $\overline{ADV/LD}$ is low, no new memory operation can be initiated. However, any pending data transfers (reads or writes) will be completed. The data bus will tri-state one cycle after the chip is deselected or a write is initiated.

The IDT71T75702/902 have an on-chip burst counter. In the burst mode, the IDT71T75702/902 can provide four cycles of data for a single address presented to the SRAM. The order of the burst sequence is defined by the \overline{LBO} input pin. The \overline{LBO} pin selects between linear and interleaved burst sequence. The $\overline{ADV/LD}$ signal is used to load a new external address ($\overline{ADV/LD} = \text{LOW}$) or increment the internal burst counter ($\overline{ADV/LD} = \text{HIGH}$).

The IDT71T75702/902 SRAMs utilize IDT's high-performance CMOS process, and are packaged in a JEDEC Standard 14mm x 20mm 100-pin plastic thin quad flatpack (TQFP) as well as a 119 ball grid array (BGA).

Pin Description Summary

A0-A19	Address Inputs	Input	Synchronous
$\overline{CE1}$, $\overline{CE2}$, $\overline{CE3}$	Chip Enables	Input	Synchronous
\overline{OE}	Output Enable	Input	Asynchronous
R/W	Read/Write Signal	Input	Synchronous
\overline{CEN}	Clock Enable	Input	Synchronous
BW1, BW2, BW3, BW4	Individual Byte Write Selects	Input	Synchronous
CLK	Clock	Input	N/A
$\overline{ADV/LD}$	Advance Burst Address/Load New Address	Input	Synchronous
\overline{LBO}	Linear/Interleaved Burst Order	Input	Static
TMS	Test Mode Select	Input	N/A
TDI	Test Data Input	Input	N/A
TCK	Test Clock	Input	N/A
TDO	Test Data Output	Output	N/A
\overline{TRST}	JTAG Reset (Optional)	Input	Asynchronous
ZZ	Sleep Mode	Input	Synchronous
I/O0-I/O31, I/OP1-I/OP4	Data Input/Output	I/O	Synchronous
VDD, VDDO	Core Power, I/O Power	Supply	Static
VSS	Ground	Supply	Static

Pin Definitions⁽¹⁾

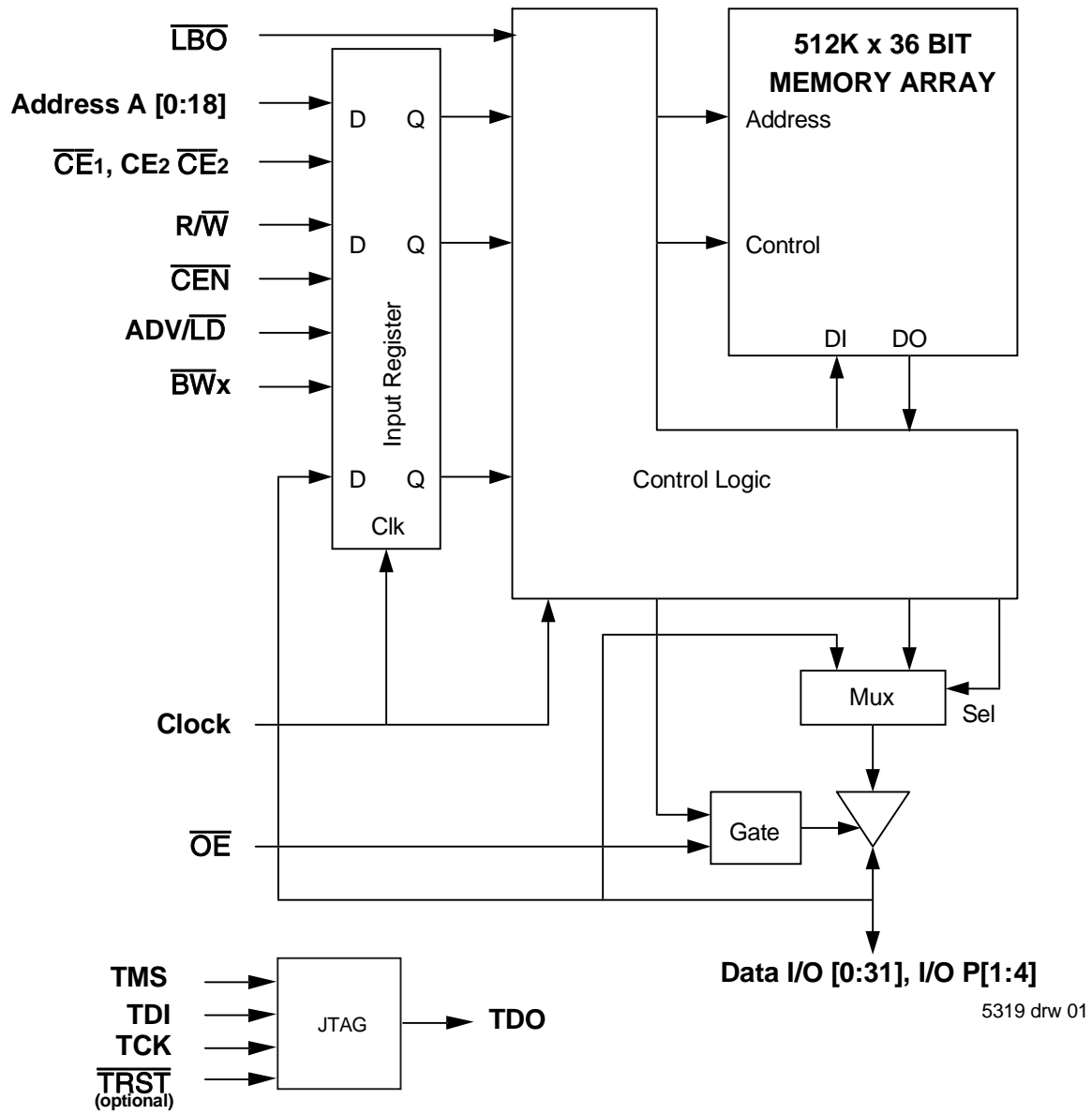
Symbol	Pin Function	I/O	Active	Description
A0-A19	Address Inputs	I	N/A	Synchronous Address inputs. The address register is triggered by a combination of the rising edge of CLK, ADV/LD low, CEN low, and true chip enables.
ADV/LD	Advance / Load	I	N/A	ADV/LD is a synchronous input that is used to load the internal registers with new address and control when it is sampled low at the rising edge of clock with the chip selected. When ADV/LD is low with the chip deselected, any burst in progress is terminated. When ADV/LD is sampled high then the internal burst counter is advanced for any burst that was in progress. The external addresses are ignored when ADV/LD is sampled high.
R/W	Read / Write	I	N/A	R/W signal is a synchronous input that identifies whether the current load cycle initiated is a Read or Write access to the memory array. The data bus activity for the current cycle takes place one clock cycle later.
CEN	Clock Enable	I	LOW	Synchronous Clock Enable Input. When CEN is sampled high, all other synchronous inputs, including clock are ignored and outputs remain unchanged. The effect of CEN sampled high on the device outputs is as if the low to high clock transition did not occur. For normal operation, CEN must be sampled low at rising edge of clock.
BW _i -BW ₄	Individual Byte Write Enables	I	LOW	Synchronous byte write enables. Each 9-bit byte has its own active low byte write enable. On load write cycles (When R/W and ADV/LD are sampled low) the appropriate byte write signal (BW _i -BW ₄) must be valid. The byte write signal must also be valid on each cycle of a burst write. Byte Write signals are ignored when R/W is sampled high. The appropriate byte(s) of data are written into the device one cycle later. BW _i -BW ₄ can all be tied low if always doing write to the entire 36-bit word.
CE ₁ , CE ₂	Chip Enables	I	LOW	Synchronous active low chip enable. CE ₁ and CE ₂ are used with CE ₂ to enable the IDT71T75702/902 (CE ₁ or CE ₂ sampled high or CE ₂ sampled low) and ADV/LD low at the rising edge of clock, initiates a deselect cycle. The ZBT™ has a one cycle deselect, i.e., the data bus will tri-state one clock cycle after deselect is initiated.
CE ₂	Chip Enable	I	HIGH	Synchronous active high chip enable. CE ₂ is used with CE ₁ and CE ₂ to enable the chip. CE ₂ has inverted polarity but otherwise identical to CE ₁ and CE ₂ .
CLK	Clock	I	N/A	This is the clock input to the IDT71T75702/902. Except for OE, all timing references for the device are made with respect to the rising edge of CLK.
I/O ₀ -I/O ₃₁ I/OP ₁ -I/OP ₄	Data Input/Output	I/O	N/A	Data input/output (I/O) pins. The data input path is registered, triggered by the rising edge of CLK. The data output path is flow-through (no output register).
LBO	Linear Burst Order	I	LOW	Burst order selection input. When LBO is high the Interleaved burst sequence is selected. When LBO is low the Linear burst sequence is selected. LBO is a static input, and it must not change during device operation.
OE	Output Enable	I	LOW	Asynchronous output enable. OE must be low to read data from the IDT71T75702/902. When OE is HIGH the I/O pins are in a high-impedance state. OE does not need to be actively controlled for read and write cycles. In normal operation, OE can be tied low.
TMS	Test Mode Select	I	N/A	Gives input command for TAP controller; sampled on rising edge of TCK. This pin has an internal pullup.
TDI	Test Data Input	I	N/A	Serial input of registers placed between TDI and TDO. Sampled on rising edge of TCK. This pin has an internal pullup.
TCK	Test Clock	I	N/A	Clock input of TAP controller. Each TAP event is clocked. Test inputs are captured on rising edge of TCK, while test outputs are driven from falling edge of TCK. This pin has an internal pullup.
TDO	Test Data Output	O	N/A	Serial output of registers placed between TDI and TDO. This output is active depending on the state of the TAP controller.
TRST	JTAG Reset (Optional)	I	LOW	Optional asynchronous JTAG reset. Can be used to reset the TAP controller, but not required. JTAG reset occurs automatically at power up and also resets using TMS and TCK per IEEE 1149.1. If not used TRST can be left floating. This pin has an internal pullup. Only available in BGA package.
ZZ	Sleep Mode	I	HIGH	Synchronous sleep mode input. ZZ HIGH will gate the CLK internally and power down the IDT71T75702/902 to its lowest power consumption level. Data retention is guaranteed in Sleep Mode. This pin has an internal pulldown.
VDD	Power Supply	N/A	N/A	2.5V core power supply.
VDDQ	Power Supply	N/A	N/A	2.5V I/O Supply.
VSS	Ground	N/A	N/A	Ground.

NOTE:

5319 tbl 02

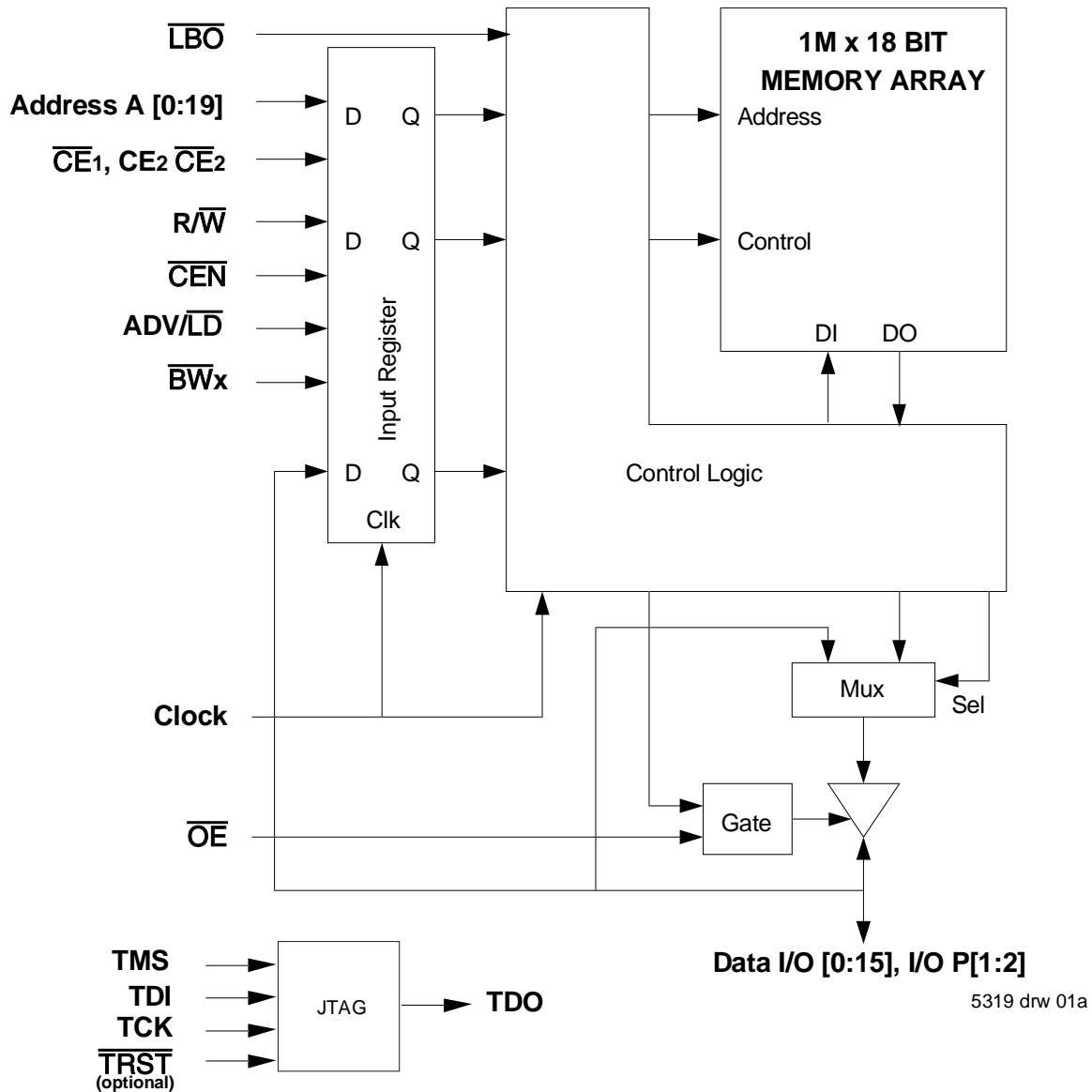
1. All synchronous inputs must meet specified setup and hold times with respect to CLK.

Functional Block Diagram — 512K x 36



5319 drw 01

Functional Block Diagram — 1M x 18



Recommended DC Operating Conditions

Symbol	Parameter	Min.	Typ.	Max.	Unit
V _{DD}	Core Supply Voltage	2.375	2.5	2.625	V
V _{DDQ}	I/O Supply Voltage	2.375	2.5	2.625	V
V _{SS}	Ground	0	0	0	V
V _{IH}	Input High Voltage — Inputs	1.7	—	V _{DD} + 0.3	V
V _{IH}	Input High Voltage — I/O	1.7	—	V _{DDQ} + 0.3 ⁽²⁾	V
V _{IL}	Input Low Voltage	-0.3 ⁽¹⁾	—	0.7	V

5319 tbl 03

NOTE:

1. V_{IL} (min.) = -0.8V for pulse width less than t_{cv}/2, once per cycle.

Recommended Operating Temperature and Supply Voltage

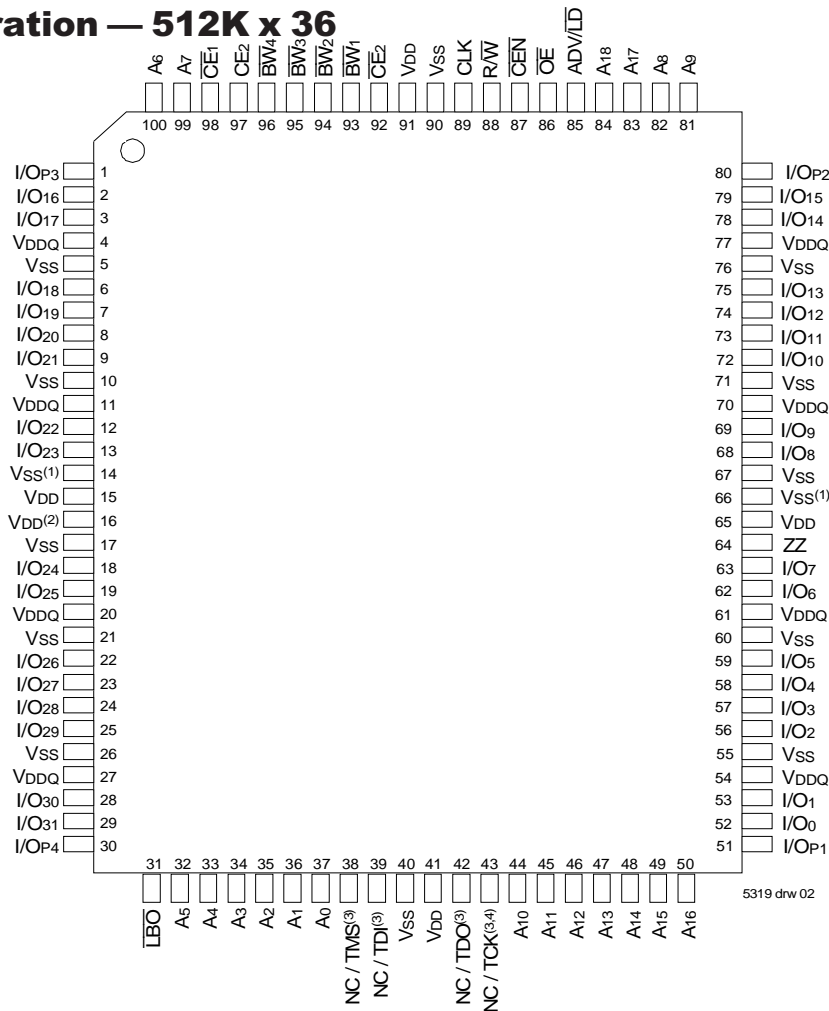
Grade	Ambient Temperature ⁽¹⁾	V _{SS}	V _{DD}	V _{DDQ}
Commerical	0 °C to +70 °C	OV	2.5V ± 5%	2.5V ± 5%
Industrial	-40 °C to +85 °C	OV	2.5V ± 5%	2.5V ± 5%

NOTE:

5319 tbl 05

1. During production testing, the case temperature equals the ambient temperature.

Pin Configuration — 512K x 36

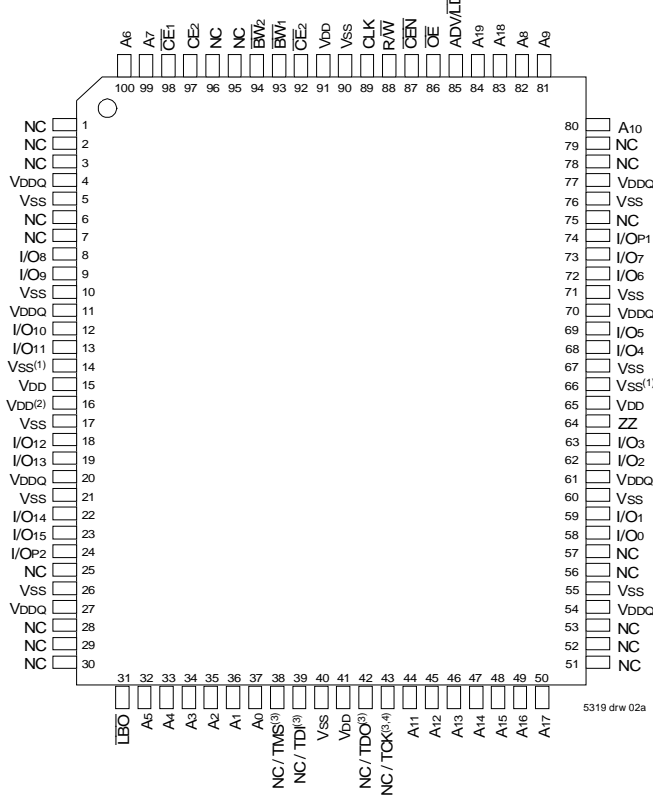


Top View 100 TQFP

NOTES:

1. Pins 14 and 66 do not have to be connected directly to V_{SS} as long as the input voltage is ≤ V_{IL}.
2. Pin 16 does not have to be connected directly to V_{DD} as long as the input voltage is ≥ V_{IH}.
3. Pins 38, 39 and 43 will be pulled internally to V_{DD} if not actively driven. To disable the TAP controller without interfering with normal operation, several settings are possible. Pins 38, 39 and 43 could be tied to V_{DD} or V_{SS} and pin 42 should be left unconnected. Or all JTAG inputs (TMS, TDI and TCK) pins 38, 39 and 43 could be left unconnected "NC" and the JTAG circuit will remain disabled from power up.
4. Pin 43 is reserved for the 36M address. JTAG is not offered in the 100-pin TQFP package for the 36M ZBT device.

Pin Configuration — 1M x 18



Top View 100 TQFP

NOTES:

- Pins 14 and 66 do not have to be connected directly to VSS as long as the input voltage is $\leq V_{IL}$.
- Pin 16 does not have to be connected directly to VDD as long as the input voltage is $\geq V_{IH}$.
- Pins 38, 39 and 43 will be pulled internally to VDD if not actively driven. To disable the TAP controller without interfering with normal operation, several settings are possible. Pins 38, 39 and 43 could be tied to VDD or VSS and pin 42 should be left unconnected. Or all JTAG inputs (TMS, TDI and TCK) pins 38, 39 and 43 could be left unconnected "NC" and the JTAG circuit will remain disabled from power up.
- Pin 43 is reserved for the 36M address. JTAG is not offered in the 100-pin TQFP package for the 36M ZBT device.

TQFP Capacitance

(TA = +25°C, f = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 3dV	5	pF
C _{I/O}	I/O Capacitance	V _{OUT} = 3dV	7	pF

5319 tbl 07

BGA Capacitance

(TA = +25°C, f = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 3dV	7	pF
C _{I/O}	I/O Capacitance	V _{OUT} = 3dV	7	pF

5319 tbl 07a

NOTE:

- This parameter is guaranteed by device characterization, but not production tested.

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial	Industrial	Unit
V _{TERM} ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +3.6	-0.5 to +3.6	V
V _{TERM} ^(3,6)	Terminal Voltage with Respect to GND	-0.5 to V _{DD}	-0.5 to V _{DD}	V
V _{TERM} ^(4,6)	Terminal Voltage with Respect to GND	-0.5 to V _{DD} +0.5	-0.5 to V _{DD} +0.5	V
V _{TERM} ^(5,6)	Terminal Voltage with Respect to GND	-0.5 to V _{DDQ} +0.5	-0.5 to V _{DDQ} +0.5	V
T _A ⁽⁷⁾	Operating Ambient Temperature	0 to +70	-40 to +85	°C
T _{BIAS}	Temperature Under Bias	-55 to +125	-55 to +125	°C
T _{STG}	Storage Temperature	-55 to +125	-55 to +125	°C
PT	Power Dissipation	2.0	2.0	W
I _{OUT}	DC Output Current	50	50	mA

5319 tbl 06

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- V_{DD} terminals only.
- V_{DDQ} terminals only.
- Input terminals only.
- I/O terminals only.
- This is a steady-state DC parameter that applies after the power supply has reached its nominal operating value. Power sequencing is not necessary; however, the voltage on any input or I/O pin cannot exceed V_{DDQ} during power supply ramp up.
- During production testing, the case temperature equals T_A.

fbGA Capacitance

(TA = +25°C, f = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 3dV	7	pF
C _{I/O}	I/O Capacitance	V _{OUT} = 3dV	7	pF

5319 tbl 07b

Pin Configuration — 512K x 36, 119 BGA(1,2,3,4)

	1	2	3	4	5	6	7
A	VDDQ	A ₆	A ₄	A ₁₈	A ₈	A ₁₆	VDDQ
B	NC	CE ₂	A ₃	ADV/LD	A ₉	CE ₂	NC
C	NC	A ₇	A ₂	VDD	A ₁₂	A ₁₅	NC
D	I/O ₁₆	I/O _{P3}	VSS	NC	VSS	I/O _{P2}	I/O ₁₅
E	I/O ₁₇	I/O ₁₈	VSS	CE ₁	VSS	I/O ₁₃	I/O ₁₄
F	VDDQ	I/O ₁₉	VSS	OE	VSS	I/O ₁₂	VDDQ
G	I/O ₂₀	I/O ₂₁	BW ₃	A ₁₇	BW ₂	I/O ₁₁	I/O ₁₀
H	I/O ₂₂	I/O ₂₃	VSS	RW	VSS	I/O ₉	I/O ₈
J	VDDQ	VDD	VDD ⁽²⁾	VDD	VSS ⁽¹⁾	VDD	VDDQ
K	I/O ₂₄	I/O ₂₆	VSS	CLK	VSS	I/O ₆	I/O ₇
L	I/O ₂₅	I/O ₂₇	BW ₄	NC	BW ₁	I/O ₄	I/O ₅
M	VDDQ	I/O ₂₈	VSS	CEN	VSS	I/O ₃	VDDQ
N	I/O ₂₉	I/O ₃₀	VSS	A ₁	VSS	I/O ₂	I/O ₁
P	I/O ₃₁	I/O _{P4}	VSS	A ₀	VSS	I/O _{P1}	I/O ₀
R	NC	A ₅	LB0	VDD	VSS ⁽¹⁾	A ₁₃	NC
T	NC	NC	A ₁₀	A ₁₁	A ₁₄	NC ⁽⁴⁾	ZZ
U	VDDQ	NC/TMS ⁽³⁾	NC/TDI ⁽³⁾	NC/TCK ⁽³⁾	NC/TDO ⁽³⁾	NC/TRST ^(3,5)	VDDQ

5319 tbl 25

Top View

Pin Configurations — 1M x 18, 119 BGA(1,2,3,4)

	1	2	3	4	5	6	7
A	VDDQ	A ₆	A ₄	A ₁₉	A ₈	A ₁₆	VDDQ
B	NC	CE ₂	A ₃	ADV/LD	A ₉	CE ₂	NC
C	NC	A ₇	A ₂	VDD	A ₁₃	A ₁₇	NC
D	I/O ₆	NC	VSS	NC	VSS	I/O _{P1}	NC
E	NC	I/O ₉	VSS	CE ₁	VSS	NC	I/O ₇
F	VDDQ	NC	VSS	OE	VSS	I/O ₆	VDDQ
G	NC	I/O ₁₀	BW ₂	A ₁₈	VSS	NC	I/O ₅
H	I/O ₁₁	NC	VSS	RW	VSS	I/O ₄	NC
J	VDDQ	VDD	VDD ⁽²⁾	VDD	VSS ⁽¹⁾	VDD	VDDQ
K	NC	I/O ₁₂	VSS	CLK	VSS	NC	I/O ₃
L	I/O ₁₃	NC	VSS	NC	BW ₁	I/O ₂	NC
M	VDDQ	I/O ₁₄	VSS	CEN	VSS	NC	VDDQ
N	I/O ₁₅	NC	VSS	A ₁	VSS	I/O ₁	NC
P	NC	I/O _{P2}	VSS	A ₀	VSS	NC	I/O ₀
R	NC	A ₅	LB0	VDD	VSS ⁽¹⁾	A ₁₂	NC
T	NC	A ₁₀	A ₁₅	NC ⁽⁴⁾	A ₁₄	A ₁₁	ZZ
U	VDDQ	NC/TMS ⁽³⁾	NC/TDI ⁽³⁾	NC/TCK ⁽³⁾	NC/TDO ⁽³⁾	NC/TRST ^(3,5)	VDDQ

5319 tbl 25a

NOTES:

Top View

1. Pins R5 and J5 do not have to be connected directly to Vss as long as the input voltage is $\leq V_{IL}$.
2. Pin J3 does not have to be connected directly to VDD as long as the input voltage is $\geq V_{IH}$.
3. U2, U3, U4 and U6 will be pulled internally to VDD if not actively driven. To disable the TAP controller without interfering with normal operation, several settings are possible. U2, U3, U4 and U6 could be tied to VDD or VSS and U5 should be left unconnected. Or all JTAG inputs(TMS, TDI, and TCK and TRST) U2, U3, U4 and U6 could be left unconnected "NC" and the JTAG circuit will remain disabled from power up.
4. The 36M address will be ball T6 (for the 512K x 36 device) and ball T4 (for the 1M x 18 device).
5. TRST is offered as an optional JTAG reset if required in the application. If not needed, can be left floating and will internally be pulled to VDD.

Synchronous Truth Table⁽¹⁾

\overline{CEN}	R/W	$\overline{CE}_1, \overline{CE}_2^{(5)}$	ADV/LD	\overline{BW}_x	ADDRESS USED	PREVIOUS CYCLE	CURRENT CYCLE	I/O (One cycle later)
L	L	L	L	Valid	External	X	LOAD WRITE	D ⁽⁷⁾
L	H	L	L	X	External	X	LOAD READ	Q ⁽⁷⁾
L	X	X	H	Valid	Internal	LOAD WRITE / BURST WRITE	BURST WRITE (Advance burst counter) ⁽²⁾	D ⁽⁷⁾
L	X	X	H	X	Internal	LOAD READ / BURST READ	BURST READ (Advance burst counter) ⁽²⁾	Q ⁽⁷⁾
L	X	H	L	X	X	X	DESELECT or STOP ⁽³⁾	HIZ
L	X	X	H	X	X	DESELECT / NOOP	NOOP	HIZ
H	X	X	X	X	X	X	SUSPEND ⁽⁴⁾	Previous Value

5319 tbl 08

NOTES:

- L = V_{IL}, H = V_{IH}, X = Don't Care.
- When ADV/LD signal is sampled high, the internal burst counter is incremented. The R/W signal is ignored when the counter is advanced. Therefore the nature of the burst cycle (Read or Write) is determined by the status of the R/W signal when the first address is loaded at the beginning of the burst cycle.
- Deselect cycle is initiated when either (\overline{CE}_1 , or \overline{CE}_2 is sampled high or CE₂ is sampled low) and ADV/LD is sampled low at rising edge of clock. The data bus will tri-state one cycle after deselect is initiated.
- When \overline{CEN} is sampled high at the rising edge of clock, that clock edge is blocked from propagating through the part. The state of all the internal registers and the I/Os remains unchanged.
- To select the chip requires $\overline{CE}_1 = L$, $\overline{CE}_2 = L$ and CE₂ = H on these chip enable pins. The chip is deselected if any one of the chip enables is false.
- Device Outputs are ensured to be in High-Z during device power-up.
- Q - data read from the device, D - data written to the device.

Partial Truth Table for Writes⁽¹⁾

OPERATION	R/W	\overline{BW}_1	\overline{BW}_2	$\overline{BW}_3^{(3)}$	$\overline{BW}_4^{(3)}$
READ	H	X	X	X	X
WRITE ALL BYTES	L	L	L	L	L
WRITE BYTE 1 (I/O[0:7], I/OP1) ⁽²⁾	L	L	H	H	H
WRITE BYTE 2 (I/O[8:15], I/OP2) ⁽²⁾	L	H	L	H	H
WRITE BYTE 3 (I/O[16:23], I/OP3) ^(2,3)	L	H	H	L	H
WRITE BYTE 4 (I/O[24:31], I/OP4) ^(2,3)	L	H	H	H	L
NO WRITE	L	H	H	H	H

5319 tbl 09

NOTES:

- L = V_{IL}, H = V_{IH}, X = Don't Care.
- Multiple bytes may be selected during the same cycle.
- N/A for x18 configuration.

Interleaved Burst Sequence Table ($\overline{LBO} = V_{DD}$)

	Sequence 1		Sequence 2		Sequence 3		Sequence 4	
	A1	A0	A1	A0	A1	A0	A1	A0
First Address	0	0	0	1	1	0	1	1
Second Address	0	1	0	0	1	1	1	0
Third Address	1	0	1	1	0	0	0	1
Fourth Address ⁽¹⁾	1	1	1	0	0	1	0	0

5319 tbl 10

NOTE:

- Upon completion of the Burst sequence the counter wraps around to its initial state and continues counting.

Linear Burst Sequence Table ($\overline{\text{LBO}}=\text{Vss}$)

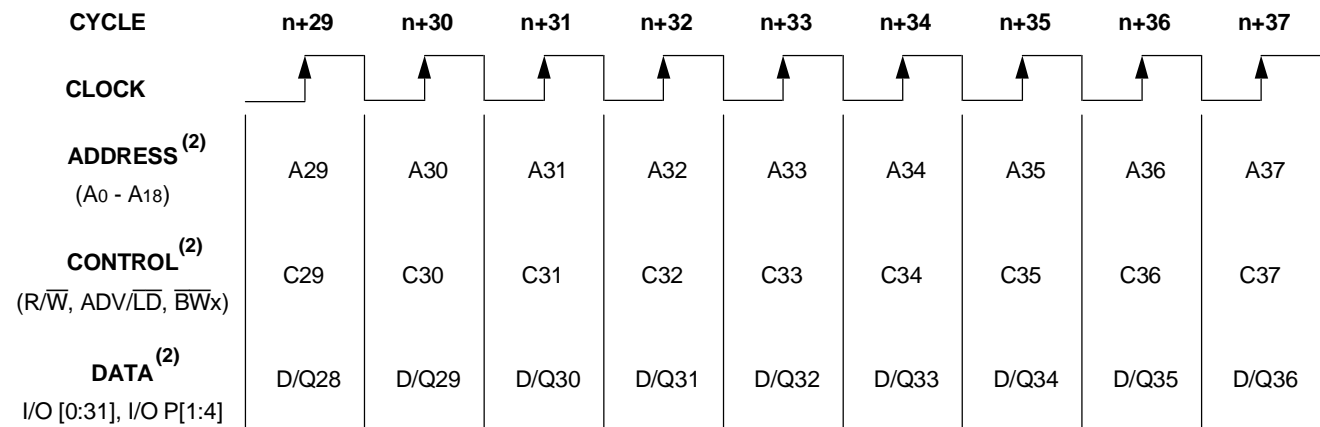
	Sequence 1		Sequence 2		Sequence 3		Sequence 4	
	A1	A0	A1	A0	A1	A0	A1	A0
First Address	0	0	0	1	1	0	1	1
Second Address	0	1	1	0	1	1	0	0
Third Address	1	0	1	1	0	0	0	1
Fourth Address ⁽¹⁾	1	1	0	0	0	1	1	0

5319 tbl 11

NOTE:

1. Upon completion of the Burst sequence the counter wraps around to its initial state and continues counting.

Functional Timing Diagram⁽¹⁾



5319 drw 03

NOTES:

1. This assumes $\overline{\text{CEN}}$, $\overline{\text{CE}}_1$, CE_2 and $\overline{\text{CE}}_2$ are all true.
2. All Address, Control and Data_In are only required to meet set-up and hold time with respect to the rising edge of clock. Data_Out is valid after a clock-to-data delay from the rising edge of clock.

Device Operation - Showing Mixed Load, Burst, Deselect and NOOP Cycles⁽²⁾

Cycle	Address	R/ \bar{W}	ADV/ $\bar{L}\bar{D}$	$\bar{C}\bar{E}_1^{(1)}$	$\bar{C}\bar{E}_N$	$\bar{B}\bar{W}_x$	$\bar{O}\bar{E}$	I/O	Comments
n	A ₀	H	L	L	L	X	X	D ₁	Load read
n+1	X	X	H	X	L	X	L	Q ₀	Burst read
n+2	A ₁	H	L	L	L	X	L	Q ₀₊₁	Load read
n+3	X	X	L	H	L	X	L	Q ₁	Deselect or STOP
n+4	X	X	H	X	L	X	X	Z	NOOP
n+5	A ₂	H	L	L	L	X	X	Z	Load read
n+6	X	X	H	X	L	X	L	Q ₂	Burst read
n+7	X	X	L	H	L	X	L	Q ₂₊₁	Deselect or STOP
n+8	A ₃	L	L	L	L	L	X	Z	Load write
n+9	X	X	H	X	L	L	X	D ₃	Burst write
n+10	A ₄	L	L	L	L	L	X	D ₃₊₁	Load write
n+11	X	X	L	H	L	X	X	D ₄	Deselect or STOP
n+12	X	X	H	X	L	X	X	Z	NOOP
n+13	A ₅	L	L	L	L	L	X	Z	Load write
n+14	A ₆	H	L	L	L	X	X	D ₅	Load read
n+15	A ₇	L	L	L	L	L	L	Q ₆	Load write
n+16	X	X	H	X	L	L	X	D ₇	Burst write
n+17	A ₈	H	L	L	L	X	X	D ₇₊₁	Load read
n+18	X	X	H	X	L	X	L	Q ₈	Burst read
n+19	A ₉	L	L	L	L	L	L	Q ₈₊₁	Load write

5319 tbl 12

NOTES:

- $\bar{C}\bar{E}_2$ timing transition is identical to $\bar{C}\bar{E}_1$ signal. $\bar{C}\bar{E}_2$ timing transition is identical but inverted to the $\bar{C}\bar{E}_1$ and $\bar{C}\bar{E}_2$ signals.
- H = High; L = Low; X = Don't Care; Z = High Impedence.

Read Operation⁽¹⁾

Cycle	Address	R \bar{W}	ADV/ $\bar{L}\bar{D}$	$\bar{C}\bar{E}_1$ ⁽²⁾	$\bar{C}\bar{E}\bar{N}$	$\bar{B}\bar{W}x$	$\bar{O}\bar{E}$	I/O	Comments
n	A ₀	H	L	L	L	X	X	X	Address and Control meet setup
n+1	X	X	X	X	X	X	L	Q ₀	Contents of Address A ₀ Read Out

5319 tbl 13

NOTES:

1. H = High; L = Low; X = Don't Care; Z = High Impedance.
2. $\bar{C}\bar{E}_2$ timing transition is identical to $\bar{C}\bar{E}_1$ signal. $\bar{C}\bar{E}_2$ timing transition is identical but inverted to the $\bar{C}\bar{E}_1$ and $\bar{C}\bar{E}_2$ signals.

Burst Read Operation⁽¹⁾

Cycle	Address	R \bar{W}	ADV/ $\bar{L}\bar{D}$	$\bar{C}\bar{E}_1$ ⁽²⁾	$\bar{C}\bar{E}\bar{N}$	$\bar{B}\bar{W}x$	$\bar{O}\bar{E}$	I/O	Comments
n	A ₀	H	L	L	L	X	X	X	Address and Control meet setup
n+1	X	X	H	X	L	X	L	Q ₀	Address A ₀ Read Out, Inc. Count
n+2	X	X	H	X	L	X	L	Q ₀₊₁	Address A ₀₊₁ Read Out, Inc. Count
n+3	X	X	H	X	L	X	L	Q ₀₊₂	Address A ₀₊₂ Read Out, Inc. Count
n+4	X	X	H	X	L	X	L	Q ₀₊₃	Address A ₀₊₃ Read Out, Load A ₁
n+5	A ₁	H	L	L	L	X	L	Q ₀	Address A ₀ Read Out, Inc. Count
n+6	X	X	H	X	L	X	L	Q ₁	Address A ₁ Read Out, Inc. Count
n+7	A ₂	H	L	L	L	X	L	Q ₁₊₁	Address A ₁₊₁ Read Out, Load A ₂

5319 tbl 14

NOTES:

1. H = High; L = Low; X = Don't Care; Z = High Impedance.
2. $\bar{C}\bar{E}_2$ timing transition is identical to $\bar{C}\bar{E}_1$ signal. $\bar{C}\bar{E}_2$ timing transition is identical but inverted to the $\bar{C}\bar{E}_1$ and $\bar{C}\bar{E}_2$ signals.

Write Operation⁽¹⁾

Cycle	Address	R \bar{W}	ADV/ $\bar{L}\bar{D}$	$\bar{C}\bar{E}_1$ ⁽²⁾	$\bar{C}\bar{E}\bar{N}$	$\bar{B}\bar{W}x$	$\bar{O}\bar{E}$	I/O	Comments
n	A ₀	L	L	L	L	L	X	X	Address and Control meet setup
n+1	X	X	X	X	L	X	X	D ₀	Write to Address A ₀

5319 tbl 15

NOTES:

1. H = High; L = Low; X = Don't Care; Z = High Impedance.
2. $\bar{C}\bar{E}_2$ timing transition is identical to $\bar{C}\bar{E}_1$ signal. $\bar{C}\bar{E}_2$ timing transition is identical but inverted to the $\bar{C}\bar{E}_1$ and $\bar{C}\bar{E}_2$ signals.

Burst Write Operation⁽¹⁾

Cycle	Address	R \bar{W}	ADV/ $\bar{L}\bar{D}$	$\bar{C}\bar{E}_1$ ⁽²⁾	$\bar{C}\bar{E}\bar{N}$	$\bar{B}\bar{W}x$	$\bar{O}\bar{E}$	I/O	Comments
n	A ₀	L	L	L	L	L	X	X	Address and Control meet setup
n+1	X	X	H	X	L	L	X	D ₀	Address A ₀ Write, Inc. Count
n+2	X	X	H	X	L	L	X	D ₀₊₁	Address A ₀₊₁ Write, Inc. Count
n+3	X	X	H	X	L	L	X	D ₀₊₂	Address A ₀₊₂ Write, Inc. Count
n+4	X	X	H	X	L	L	X	D ₀₊₃	Address A ₀₊₃ Write, Load A ₁
n+5	A ₁	L	L	L	L	L	X	D ₀	Address A ₀ Write, Inc. Count
n+6	X	X	H	X	L	L	X	D ₁	Address A ₁ Write, Inc. Count
n+7	A ₂	L	L	L	L	L	X	D ₁₊₁	Address A ₁₊₁ Write, Load A ₂

5319 tbl 16

NOTES:

1. H = High; L = Low; X = Don't Care; Z = High Impedance.
2. $\bar{C}\bar{E}_2$ timing transition is identical to $\bar{C}\bar{E}_1$ signal. $\bar{C}\bar{E}_2$ timing transition is identical but inverted to the $\bar{C}\bar{E}_1$ and $\bar{C}\bar{E}_2$ signals.

Read Operation with Clock Enable Used⁽¹⁾

Cycle	Address	R \bar{W}	ADV $\bar{L}\bar{D}$	$\bar{C}\bar{E}_1$ ⁽²⁾	$\bar{C}\bar{E}\bar{N}$	$\bar{B}\bar{W}_x$	$\bar{O}\bar{E}$	I/O	Comments
n	A ₀	H	L	L	L	X	X	X	Address A ₀ and Control meet setup
n+1	X	X	X	X	H	X	X	X	Clock n+1 Ignored
n+2	A ₁	H	L	L	L	X	L	Q ₀	Address A ₀ Read out, Load A ₁
n+3	X	X	X	X	H	X	L	Q ₀	Clock Ignored. Data Q ₀ is on the bus.
n+4	X	X	X	X	H	X	L	Q ₀	Clock Ignored. Data Q ₀ is on the bus.
n+5	A ₂	H	L	L	L	X	L	Q ₁	Address A ₁ Read out, Load A ₂
n+6	A ₃	H	L	L	L	X	L	Q ₂	Address A ₂ Read out, Load A ₃
n+7	A ₄	H	L	L	L	X	L	Q ₃	Address A ₃ Read out, Load A ₄

5319 tbl 17

NOTES:

1. H = High; L = Low; X = Don't Care; Z = High Impedance.
2. $\bar{C}\bar{E}_2$ timing transition is identical to $\bar{C}\bar{E}_1$ signal. $\bar{C}\bar{E}_2$ timing transition is identical but inverted to the $\bar{C}\bar{E}_1$ and $\bar{C}\bar{E}_2$ signals.

Write Operation with Clock Enable Used⁽¹⁾

Cycle	Address	R \bar{W}	ADV $\bar{L}\bar{D}$	$\bar{C}\bar{E}_1$ ⁽²⁾	$\bar{C}\bar{E}\bar{N}$	$\bar{B}\bar{W}_x$	$\bar{O}\bar{E}$	I/O	Comments
n	A ₀	L	L	L	L	L	X	X	Address A ₀ and Control meet setup.
n+1	X	X	X	X	H	X	X	X	Clock n+1 Ignored.
n+2	A ₁	L	L	L	L	L	X	D ₀	Write data D ₀ , Load A ₁ .
n+3	X	X	X	X	H	X	X	X	Clock Ignored.
n+4	X	X	X	X	H	X	X	X	Clock Ignored.
n+5	A ₂	L	L	L	L	L	X	D ₁	Write Data D ₁ , Load A ₂
n+6	A ₃	L	L	L	L	L	X	D ₂	Write Data D ₂ , Load A ₃
n+7	A ₄	L	L	L	L	L	X	D ₃	Write Data D ₃ , Load A ₄

5319 tbl 18

NOTES:

1. H = High; L = Low; X = Don't Care; Z = High Impedance.
2. $\bar{C}\bar{E}_2$ timing transition is identical to $\bar{C}\bar{E}_1$ signal. $\bar{C}\bar{E}_2$ timing transition is identical but inverted to the $\bar{C}\bar{E}_1$ and $\bar{C}\bar{E}_2$ signals.

Read Operation with Chip Enable Used⁽¹⁾

Cycle	Address	R \bar{W}	ADV/ $\bar{L}\bar{D}$	$\bar{C}\bar{E}_1^{(2)}$	$\bar{C}\bar{E}\bar{N}$	$\bar{B}\bar{W}x$	$\bar{O}\bar{E}$	I/O ⁽³⁾	Comments
n	X	X	L	H	L	X	X	?	Deselected.
n+1	X	X	L	H	L	X	X	Z	Deselected.
n+2	A ₀	H	L	L	L	X	X	Z	Address A ₀ and Control meet setup.
n+3	X	X	L	H	L	X	L	Q ₀	Address A ₀ read out, Deselected.
n+4	A ₁	H	L	L	L	X	X	Z	Address A ₁ and Control meet setup.
n+5	X	X	L	H	L	X	L	Q ₁	Address A ₁ read out, Deselected.
n+6	X	X	L	H	L	X	X	Z	Deselected.
n+7	A ₂	H	L	L	L	X	X	Z	Address A ₂ and Control meet setup.
n+8	X	X	L	H	L	X	L	Q ₂	Address A ₂ read out, Deselected.
n+9	X	X	L	H	L	X	X	Z	Deselected.

5319 tbl 19

NOTES:

1. H = High; L = Low; X = Don't Care; ? = Don't Know; Z = High Impedance.
2. $\bar{C}\bar{E}_2$ timing transition is identical to $\bar{C}\bar{E}_1$ signal. CE₂ timing transition is identical but inverted to the $\bar{C}\bar{E}_1$ and $\bar{C}\bar{E}_2$ signals.
3. Device outputs are ensured to be in High-Z during device power-up.

Write Operation with Chip Enable Used⁽¹⁾

Cycle	Address	R \bar{W}	ADV/ $\bar{L}\bar{D}$	$\bar{C}\bar{E}_1^{(2)}$	$\bar{C}\bar{E}\bar{N}$	$\bar{B}\bar{W}x$	$\bar{O}\bar{E}$	I/O	Comments
n	X	X	L	H	L	X	X	?	Deselected.
n+1	X	X	L	H	L	X	X	Z	Deselected.
n+2	A ₀	L	L	L	L	L	X	Z	Address A ₀ and Control meet setup
n+3	X	X	L	H	L	X	X	D ₀	Data D ₀ Write In, Deselected.
n+4	A ₁	L	L	L	L	L	X	Z	Address A ₁ and Control meet setup
n+5	X	X	L	H	L	X	X	D ₁	Data D ₁ Write In, Deselected.
n+6	X	X	L	H	L	X	X	Z	Deselected.
n+7	A ₂	L	L	L	L	L	X	Z	Address A ₂ and Control meet setup
n+8	X	X	L	H	L	X	X	D ₂	Data D ₂ Write In, Deselected.
n+9	X	X	L	H	L	X	X	Z	Deselected.

5319 tbl 20

NOTES:

1. H = High; L = Low; X = Don't Care; ? = Don't Know; Z = High Impedance.
2. CE = L is defined as $\bar{C}\bar{E}_1 = L$, $\bar{C}\bar{E}_2 = L$ and CE₂ = H. CE = H is defined as $\bar{C}\bar{E}_1 = H$, $\bar{C}\bar{E}_2 = H$ or CE₂ = L.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (V_{DD} = 2.5V±5%)

Symbol	Parameter	Test Conditions	Min.	Max.	Unit
I _{LI}	Input Leakage Current	V _{DD} = Max., V _{IN} = 0V to V _{DD}	—	5	μA
I _{LI}	$\overline{\text{LBO}}$, JTAG and ZZ Input Leakage Current ⁽¹⁾	V _{DD} = Max., V _{IN} = 0V to V _{DD}	—	30	μA
I _{LO}	Output Leakage Current	V _{OUT} = 0V to V _{CC}	—	5	μA
V _{OL}	Output Low Voltage	I _{OL} = +6mA, V _{DD} = Min.	—	0.4	V
V _{OH}	Output High Voltage	I _{OH} = -6mA, V _{DD} = Min.	2.0	—	V

NOTE:

5319 tbl 21

1. The $\overline{\text{LBO}}$, TMS, TDI, TCK and $\overline{\text{TRST}}$ pins will be internally pulled to V_{DD} and the ZZ pin will be internally pulled to V_{SS} if they are not actively driven in the application.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽¹⁾ (V_{DD} = 2.5V±5%)

Symbol	Parameter	Test Conditions	7.5ns		8ns		8.5ns		Unit
			Com'l	Ind	Com'l	Ind	Com'l	Ind	
I _{DD}	Operating Power Supply Current	Device Selected, Outputs Open, ADV/LD = X, V _{DD} = Max., V _{IN} ≥ V _{IH} or ≤ V _{IL} , f = f _{MAX} ⁽²⁾	275	295	250	270	225	245	mA
I _{SB1}	CMOS Standby Power Supply Current	Device Deselected, Outputs Open, V _{DD} = Max., V _{IN} ≥ V _{HD} or ≤ V _{LD} , f = 0 ^(2,3)	40	60	40	60	40	60	mA
I _{SB2}	Clock Running Power Supply Current	Device Deselected, Outputs Open, V _{DD} = Max., V _{IN} ≥ V _{HD} or ≤ V _{LD} , f = f _{MAX} ^(2,3)	105	125	100	120	95	115	mA
I _{SB3}	Idle Power Supply Current	Device Selected, Outputs Open, $\overline{\text{CEN}} \geq V_{IH}$, V _{DD} = Max., V _{IN} ≥ V _{HD} or ≤ V _{LD} , f = f _{MAX} ^(2,3)	60	80	60	80	60	80	mA
I _{ZZ}	Full Sleep Mode Supply Current	Device Selected, Outputs Open, $\overline{\text{CEN}} \leq V_{IH}$, V _{DD} = Max., ZZ ≥ V _{HD} , V _{IN} ≥ V _{HD} or ≤ V _{LD} , f = f _{MAX} ^(2,3)	40	60	40	60	40	60	mA

NOTES:

5319 tbl 22

- All values are maximum guaranteed values.
- At f = f_{MAX}, inputs are cycling at the maximum frequency of read cycles of 1/tcyc; f=0 means no input lines are changing.
- For I/Os V_{HD} = V_{DDQ} - 0.2V, V_{LD} = 0.2V. For other inputs V_{HD} = V_{DD} - 0.2V, V_{LD} = 0.2V.

AC Test Load

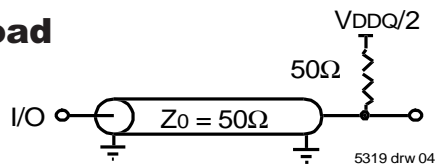


Figure 1. AC Test Load

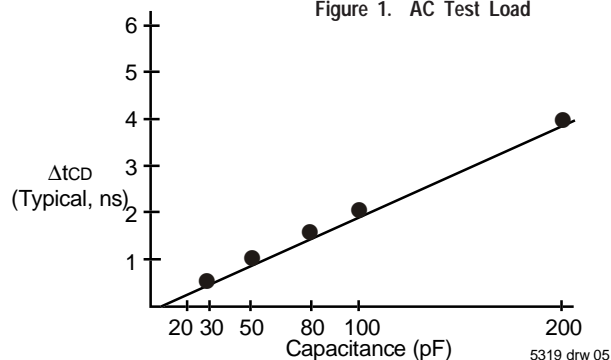


Figure 2. Lumped Capacitive Load, Typical Derating

AC Test Conditions

Input Pulse Levels	0 to 2.5V
Input Rise/Fall Times	2ns
Input Timing Reference Levels	(V _{DDQ} /2)
Output Reference Levels	(V _{DDQ} /2)
Output Load	Figure 1

5319 tbl 23

AC Electrical Characteristics

(VDD = 2.5V±5%, Commercial and Industrial Temperature Ranges)

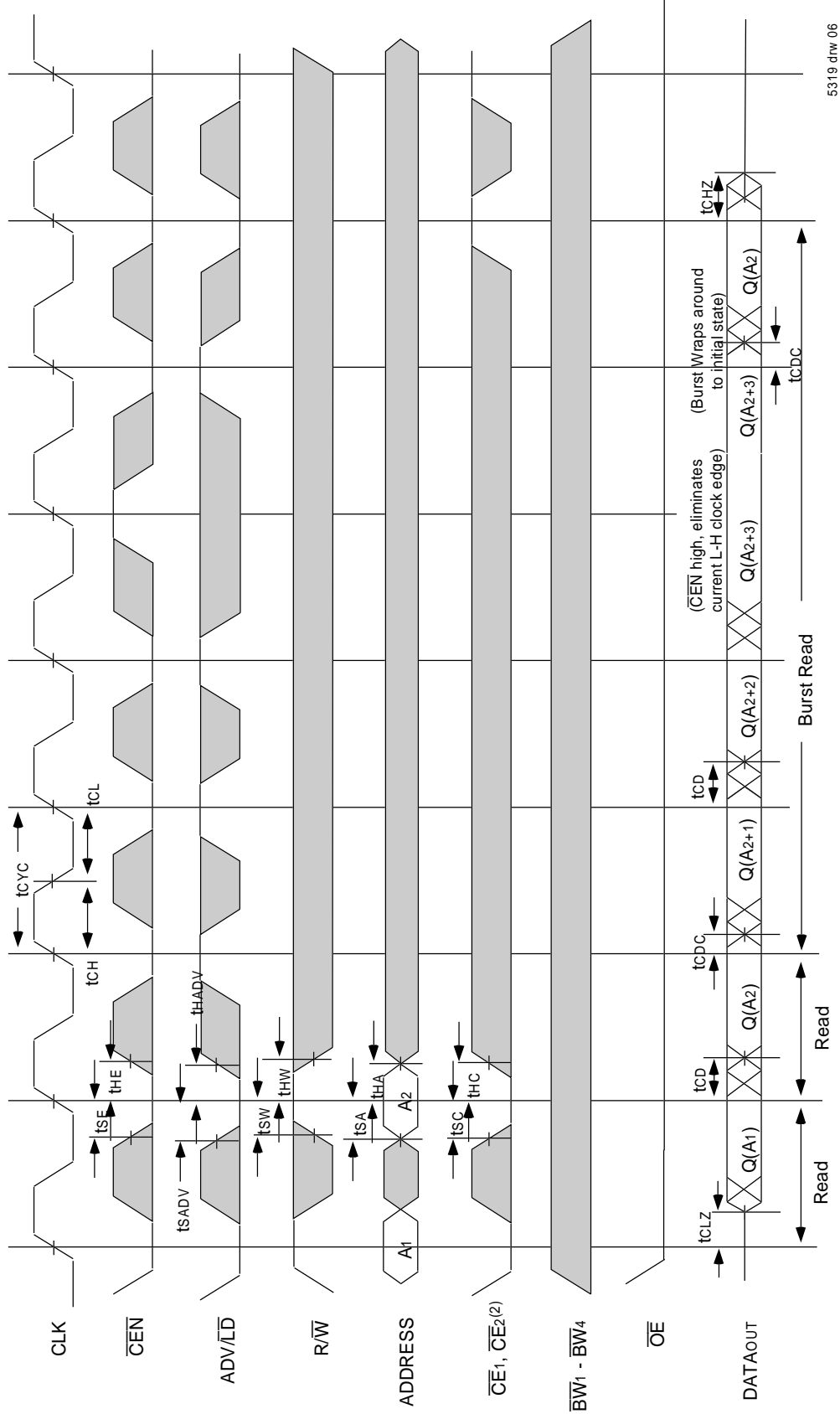
Symbol	Parameter	7.5ns		8ns		8.5ns		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
t _{CYC}	Clock Cycle Time	10	—	10.5	—	11	—	ns
t _{CH} ⁽¹⁾	Clock High Pulse Width	2.5	—	2.7	—	3.0	—	ns
t _{CL} ⁽¹⁾	Clock Low Pulse Width	2.5	—	2.7	—	3.0	—	ns
Output Parameters								
t _{CD}	Clock High to Valid Data	—	7.5	—	8	—	8.5	ns
t _{ODC}	Clock High to Data Change	2	—	2	—	2	—	ns
t _{OLZ} ^(2,3,4)	Clock High to Output Active	3	—	3	—	3	—	ns
t _{CHZ} ^(2,3,4)	Clock High to Data High-Z	—	5	—	5	—	5	ns
t _{OE}	Output Enable Access Time	—	5	—	5	—	5	ns
t _{OLZ} ^(2,3)	Output Enable Low to Data Active	0	—	0	—	0	—	ns
t _{OHZ} ^(2,3)	Output Enable High to Data High-Z	—	5	—	5	—	5	ns
Set Up Times								
t _{SE}	Clock Enable Setup Time	2.0	—	2.0	—	2.0	—	ns
t _{SA}	Address Setup Time	2.0	—	2.0	—	2.0	—	ns
t _{SD}	Data In Setup Time	2.0	—	2.0	—	2.0	—	ns
t _{SW}	Read/Write (R/W) Setup Time	2.0	—	2.0	—	2.0	—	ns
t _{ADV}	Advance/Load (ADV/LD) Setup Time	2.0	—	2.0	—	2.0	—	ns
t _{SC}	Chip Enable/Select Setup Time	2.0	—	2.0	—	2.0	—	ns
t _{SB}	Byte Write Enable (BWx) Setup Time	2.0	—	2.0	—	2.0	—	ns
Hold Times								
t _{HE}	Clock Enable Hold Time	0.5	—	0.5	—	0.5	—	ns
t _{HA}	Address Hold Time	0.5	—	0.5	—	0.5	—	ns
t _{HD}	Data In Hold Time	0.5	—	0.5	—	0.5	—	ns
t _{HW}	Read/Write (R/W) Hold Time	0.5	—	0.5	—	0.5	—	ns
t _{HADV}	Advance/Load (ADV/LD) Hold Time	0.5	—	0.5	—	0.5	—	ns
t _{HC}	Chip Enable/Select Hold Time	0.5	—	0.5	—	0.5	—	ns
t _{HB}	Byte Write Enable (BWx) Hold Time	0.5	—	0.5	—	0.5	—	ns

5319 tbl 24

NOTES:

1. Measured as HIGH above 0.6V_{DD0} and LOW below 0.4V_{DD0}.
2. Transition is measured ±200mV from steady-state.
3. These parameters are guaranteed with the AC load (Figure 1) by device characterization. They are not production tested.
4. To avoid bus contention, the output buffers are designed such that t_{CHZ} (device turn-off) is about 1ns faster than t_{CLZ} (device turn-on) at a given temperature and voltage. The specs as shown do not imply bus contention because t_{CLZ} is a Min. parameter that is worse case at totally different test conditions (0 deg. C, 2.625V) than t_{CHZ}, which is a Max. parameter (worse case at 70 deg. C, 2.375V).

Timing Waveform of Read Cycle(1,2,3,4)

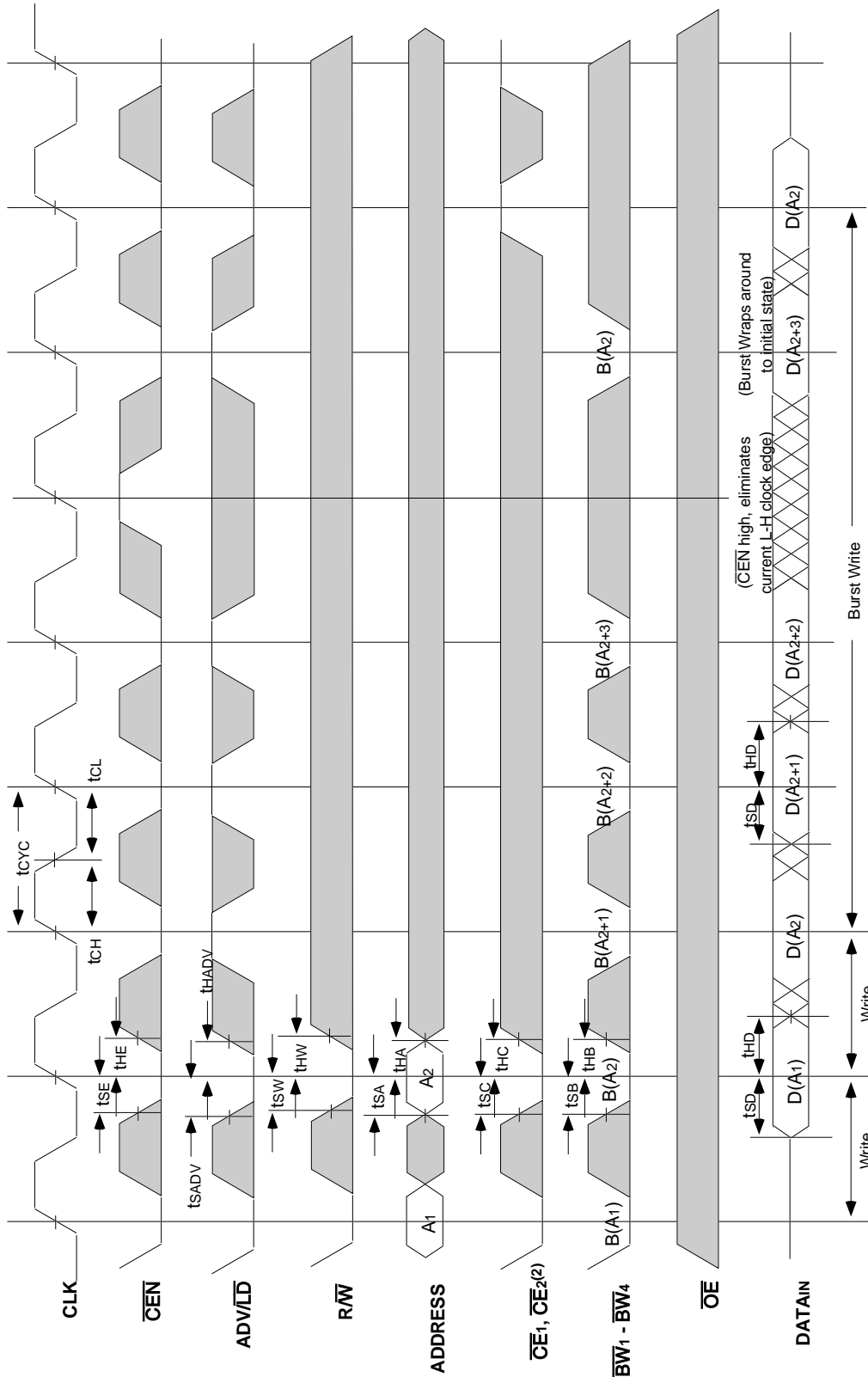


5319 drw 06

NOTES:

1. Q(A1) represents the first output from the external address A1. Q(A2) represents the first output from the external address A2. Q(A2+1) represents the next output data in the burst sequence of the base address A2, etc. where address bits A0 and A1 are advancing for the four word burst in the sequence defined by the state of the LBO input.
2. CE2 timing transitions are identical but inverted to the CE1 and CE2 signals. For example, when CE1 and CE2 are LOW on this waveform, CE2 is HIGH.
3. Burst ends when new address and control are loaded into the SRAM by sampling ADV/LD LOW.
4. R/W is don't care when the SRAM is bursting (ADV/LD sampled HIGH). The nature of the burst access (Read or Write) is fixed by the state of the R/W signal when new address and control are loaded into the SRAM.

Timing Waveform of Write Cycles(1,2,3,4,5)

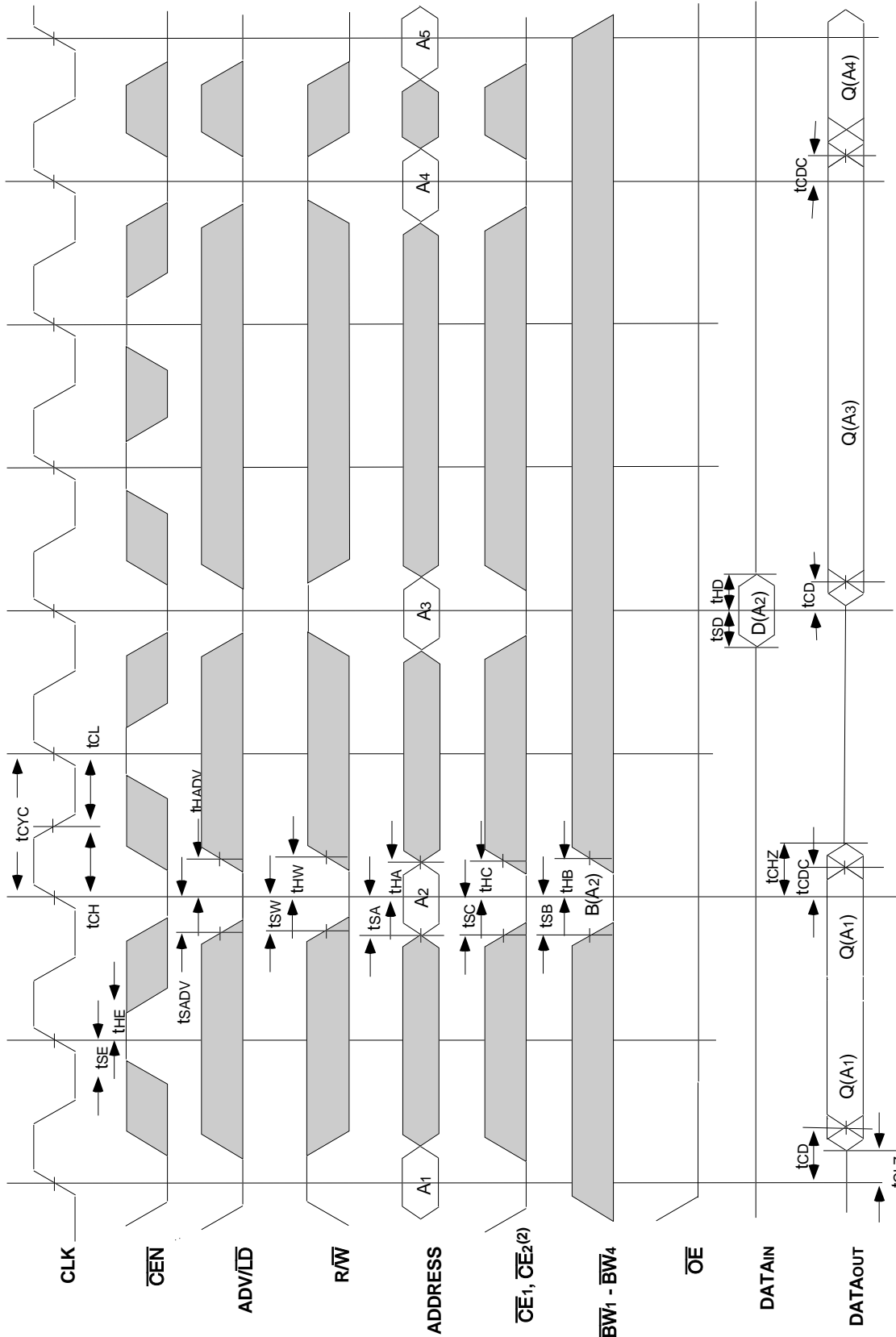


5319 clw 07

NOTES:

1. D (A1) represents the first input to the external address A1. D (A2) represents the first input to the external address A2; D (A2+1) represents the next input data in the burst sequence of the base address A2, etc. where address bits A0 and A1 are advancing for the four word burst in the sequence defined by the state of the LBO input.
2. CE2 timing transitions are identical but inverted to the CE1 and CE2 signals. For example, when CE1 and CE2 are LOW on this waveform, CE2 is HIGH.
3. Burst ends when new address and control are loaded into the SRAM by sampling ADV/LD LOW.
4. R/W is don't care when the SRAM is bursting (ADV/LD sampled HIGH). The nature of the burst access (Read or Write) is fixed by the state of the R/W signal when new address and control are loaded into the SRAM.
5. Individual Byte Write signals (BWx) must be valid on all write and burst-write cycles. A write cycle is initiated when R/W signal is sampled LOW. The byte write information comes in one cycle before the actual data is presented to the SRAM.

Timing Waveform of $\overline{\text{CEN}}$ Operation(1,2,3,4)

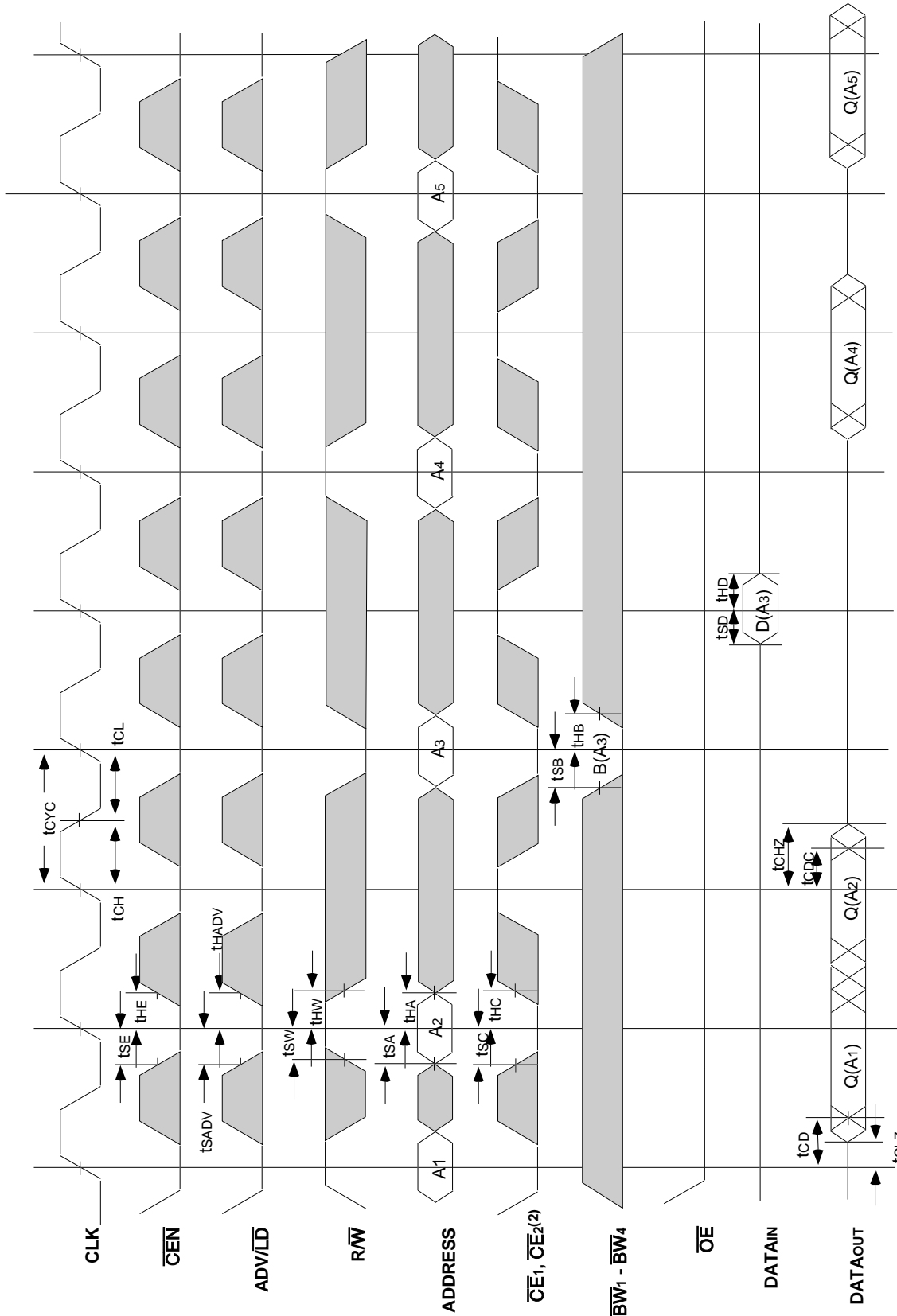


5319 drw 09

NOTES:

1. $Q(A1)$ represents the first output from the external address A1. $D(A2)$ represents the input data to the SRAM corresponding to address A2.
2. $\overline{\text{CE1}}$ and $\overline{\text{CE2}}$ timing transitions are identical but inverted to the $\overline{\text{CE1}}$ and $\overline{\text{CE2}}$ signals. For example, when $\overline{\text{CE1}}$ and $\overline{\text{CE2}}$ are LOW on this waveform, $\overline{\text{CE1}}$ and $\overline{\text{CE2}}$ are HIGH.
3. $\overline{\text{CEN}}$ when sampled high on the rising edge of clock will block that L-H transition of the clock from propagating into the SRAM. The part will behave as if the L-H clock transition did not occur. All internal registers in the SRAM will retain their previous state.
4. Individual Byte Write signals ($\overline{\text{BWx}}$) must be valid on all write and burst-write cycles. A write cycle is initiated when $\overline{\text{RW}}$ signal is sampled LOW. The byte write information comes in one cycle before the actual data is presented to the SRAM.

Timing Waveform of $\overline{\text{CS}}$ Operation(1,2,3,4)

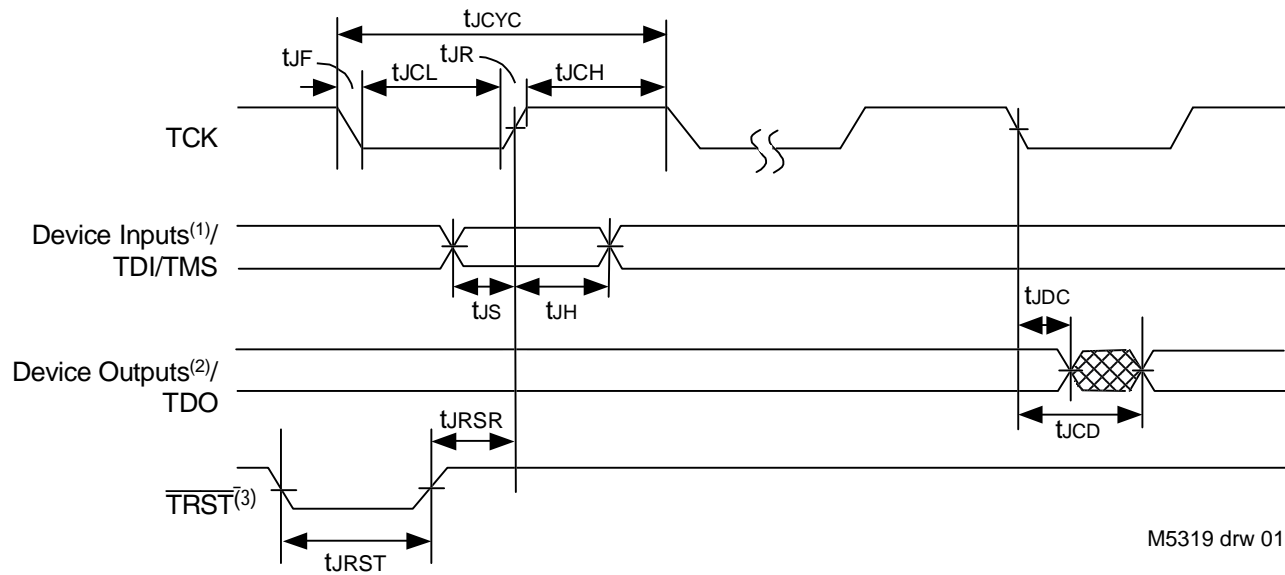


5319 drw 10

NOTES:

1. Q(A1) represents the first output from the external address A1. D(A3) represents the input data to the SRAM corresponding to address A3 etc.
2. CE2 timing transitions are identical but inverted to the $\overline{\text{CE1}}$ and $\overline{\text{CE2}}$ signals. For example, when $\overline{\text{CE1}}$ and $\overline{\text{CE2}}$ are LOW on this waveform, CE2 is HIGH.
3. When either one of the Chip enables ($\overline{\text{CE1}}$, $\overline{\text{CE2}}$) is sampled inactive at the rising clock edge, a deselect cycle is initiated. The data-bus tri-states one cycle after the initiation of the deselect cycle. This allows for any pending data transfers (reads or writes) to be completed.
4. Individual Byte Write signals ($\overline{\text{BWx}}$) must be valid on all write and burst-write cycles. A write cycle is initiated when $\overline{\text{RW}}$ signal is sampled LOW. The byte write information comes in one cycle before the actual data is presented to the SRAM.

JTAG Interface Specification



NOTES:

1. Device inputs = All device inputs except TDI, TMS and \overline{TRST} .
2. Device outputs = All device outputs except TDO.
3. During power up, \overline{TRST} could be driven low or not be used since the JTAG circuit resets automatically. \overline{TRST} is an optional JTAG reset.

JTAG AC Electrical Characteristics^(1,2,3,4)

Symbol	Parameter	Min.	Max.	Units
		t_{JCYC}	JTAG Clock Input Period	100
t_{JCH}	JTAG Clock HIGH	40	—	ns
t_{JCL}	JTAG Clock Low	40	—	ns
t_{JR}	JTAG Clock Rise Time	—	5 ⁽¹⁾	ns
t_{JF}	JTAG Clock Fall Time	—	5 ⁽¹⁾	ns
t_{TRST}	JTAG Reset	50	—	ns
t_{JRSR}	JTAG Reset Recovery	50	—	ns
t_{JCD}	JTAG Data Output	—	20	ns
t_{JDC}	JTAG Data Output Hold	0	—	ns
t_{JS}	JTAG Setup	25	—	ns
t_{JH}	JTAG Hold	25	—	ns

5319 tbl 01

NOTES:

1. Guaranteed by design.
2. AC Test Load (Fig. 1) on external output signals.
3. Refer to AC Test Conditions stated earlier in this document.
4. JTAG operations occur at one speed (10MHz). The base device may run at any speed specified in this datasheet.

Scan Register Sizes

Register Name	Bit Size
Instruction (IR)	4
Bypass (BYR)	1
JTAG Identification (JIDR)	32
Boundary Scan (BSR)	Note (1)

5319 tbl 03

NOTE:

1. The Boundary Scan Descriptive Language (BSDL) file for this device is available by contacting your local IDT sales representative.

JTAG Identification Register Definitions

Instruction Field	Value	Description
Revision Number (31:28)	0x2	Reserved for version number.
IDT Device ID (27:12)	0x221, 0x223	Defines IDT part number 71T75702 and 71T75902, respectively.
IDT JEDEC ID (11:1)	0x33	Allows unique identification of device vendor as IDT.
ID Register Indicator Bit (Bit 0)	1	Indicates the presence of an ID register.

I5319tbl 02

Available JTAG Instructions

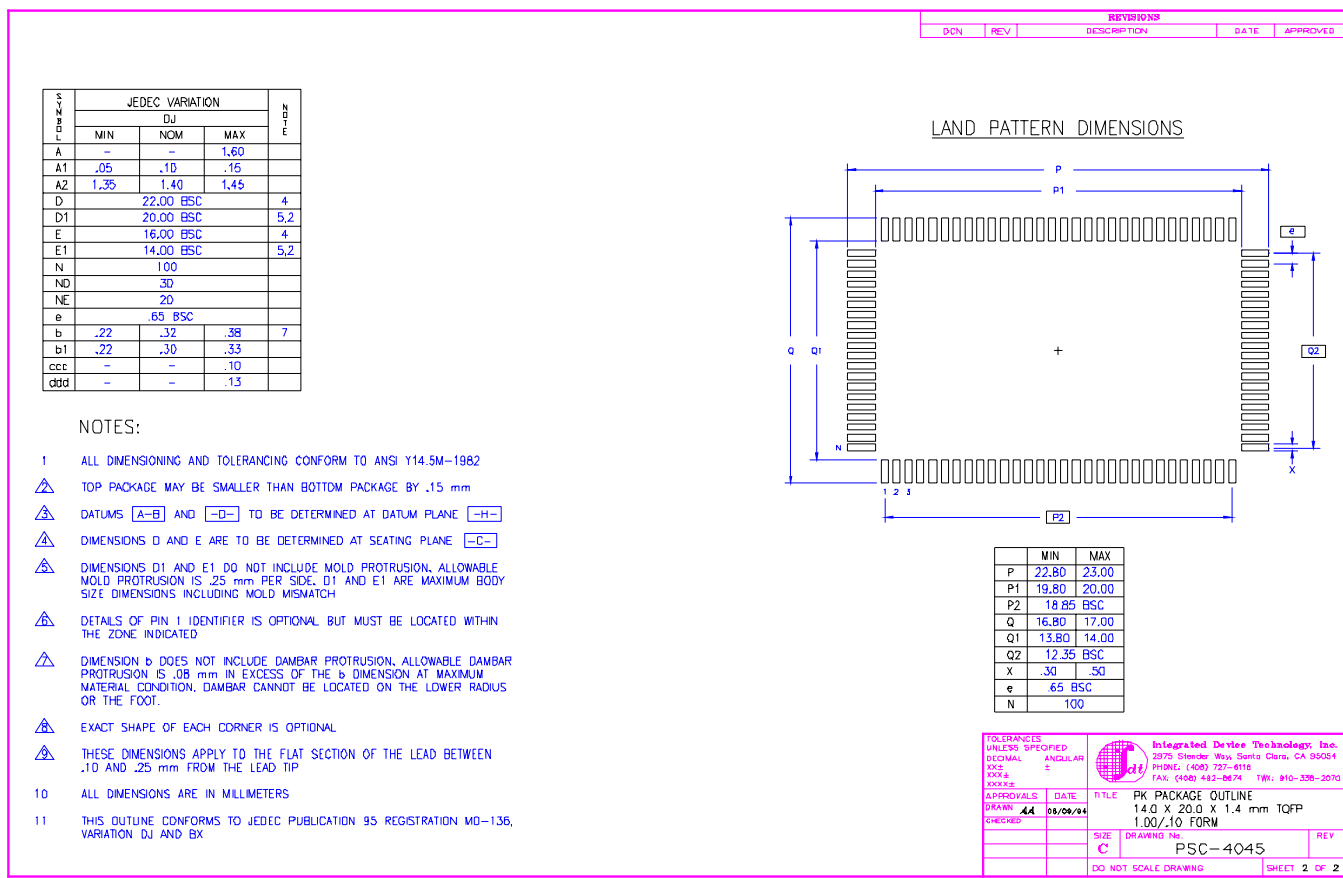
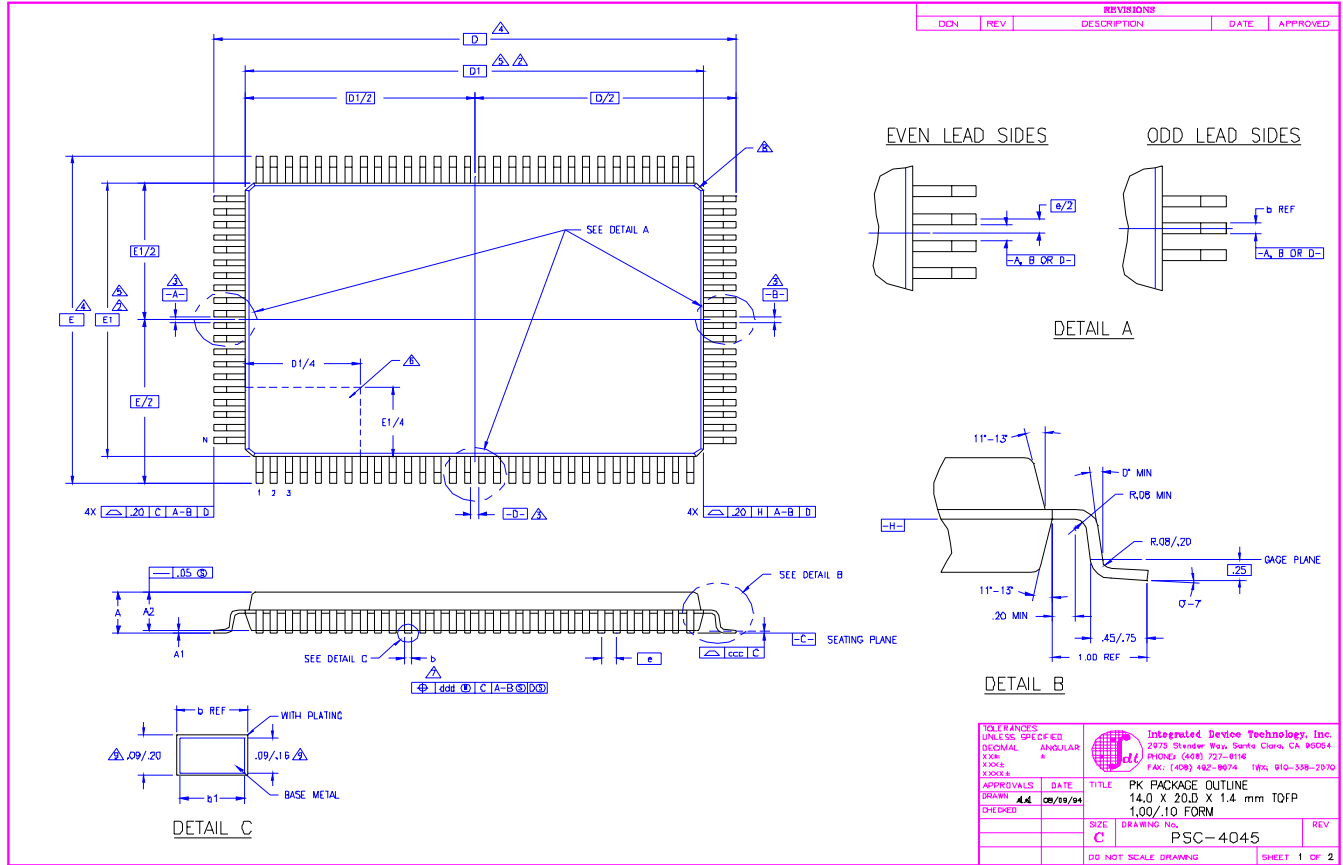
Instruction	Description	OPCODE
EXTEST	Forces contents of the boundary scan cells onto the device outputs ⁽¹⁾ . Places the boundary scan register (BSR) between TDI and TDO.	0000
SAMPLE/PRELOAD	Places the boundary scan register (BSR) between TDI and TDO. SAMPLE allows data from device inputs ⁽²⁾ and outputs ⁽¹⁾ to be captured in the boundary scan cells and shifted serially through TDO. PRELOAD allows data to be input serially into the boundary scan cells via the TDI.	0001
DEVICE_ID	Loads the JTAG ID register (JIDR) with the vendor ID code and places the register between TDI and TDO.	0010
HIGHZ	Places the bypass register (BYR) between TDI and TDO. Forces all device output drivers to a High-Z state.	0011
RESERVED	Several combinations are reserved. Do not use codes other than those identified for EXTEST, SAMPLE/PRELOAD, DEVICE_ID, HIGHZ, CLAMP, VALIDATE and BYPASS instructions.	0100
RESERVED		0101
RESERVED		0110
RESERVED		0111
CLAMP	Uses BYR. Forces contents of the boundary scan cells onto the device outputs. Places the bypass register (BYR) between TDI and TDO.	1000
RESERVED	Same as above.	1001
RESERVED		1010
RESERVED		1011
RESERVED		1100
VALIDATE	Automatically loaded into the instruction register whenever the TAP controller passes through the CAPTURE-IR state. The lower two bits '01' are mandated by the IEEE std. 1149.1 specification.	1101
RESERVED	Same as above.	1110
BYPASS	The BYPASS instruction is used to truncate the boundary scan register as a single bit in length.	1111

I5319tbl 04

NOTES:

1. Device outputs = All device outputs except TDO.
2. Device inputs = All device inputs except TDI, TMS, and \overline{TRST} .

100 Pin Thin Quad Plastic Flatpack (TQFP) Package Diagram Outline

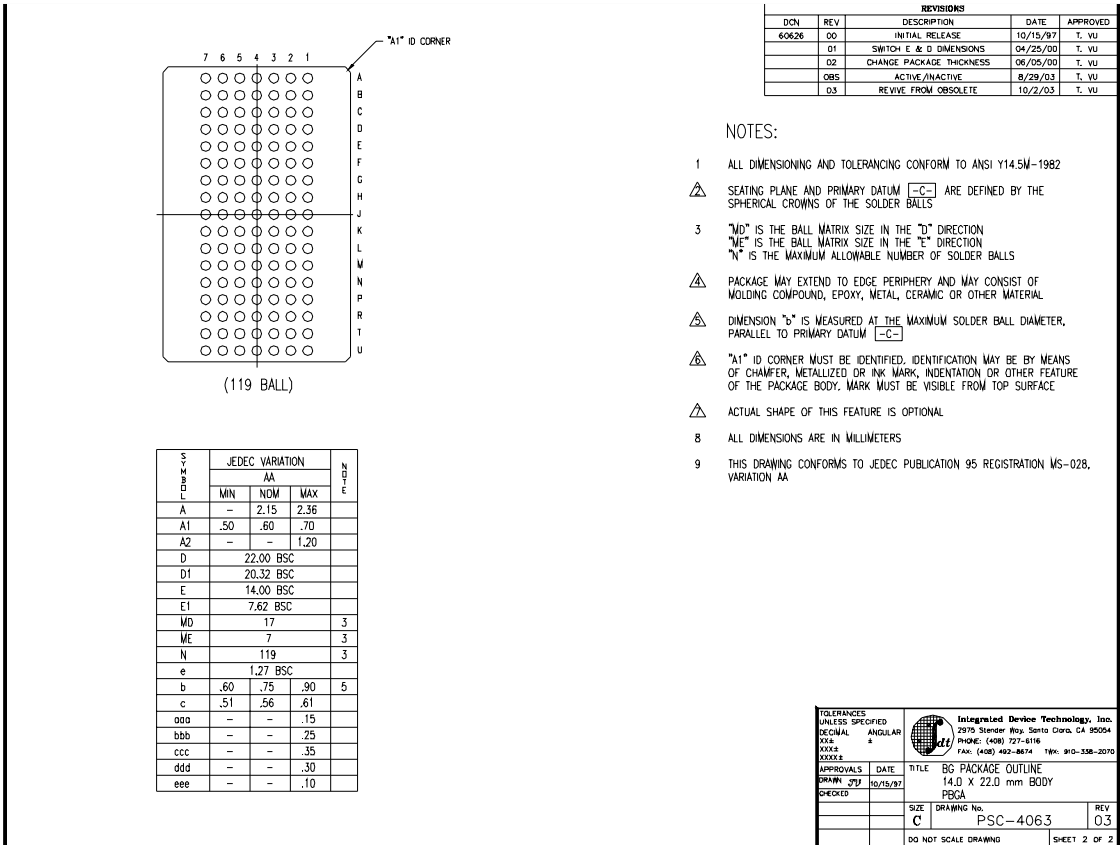
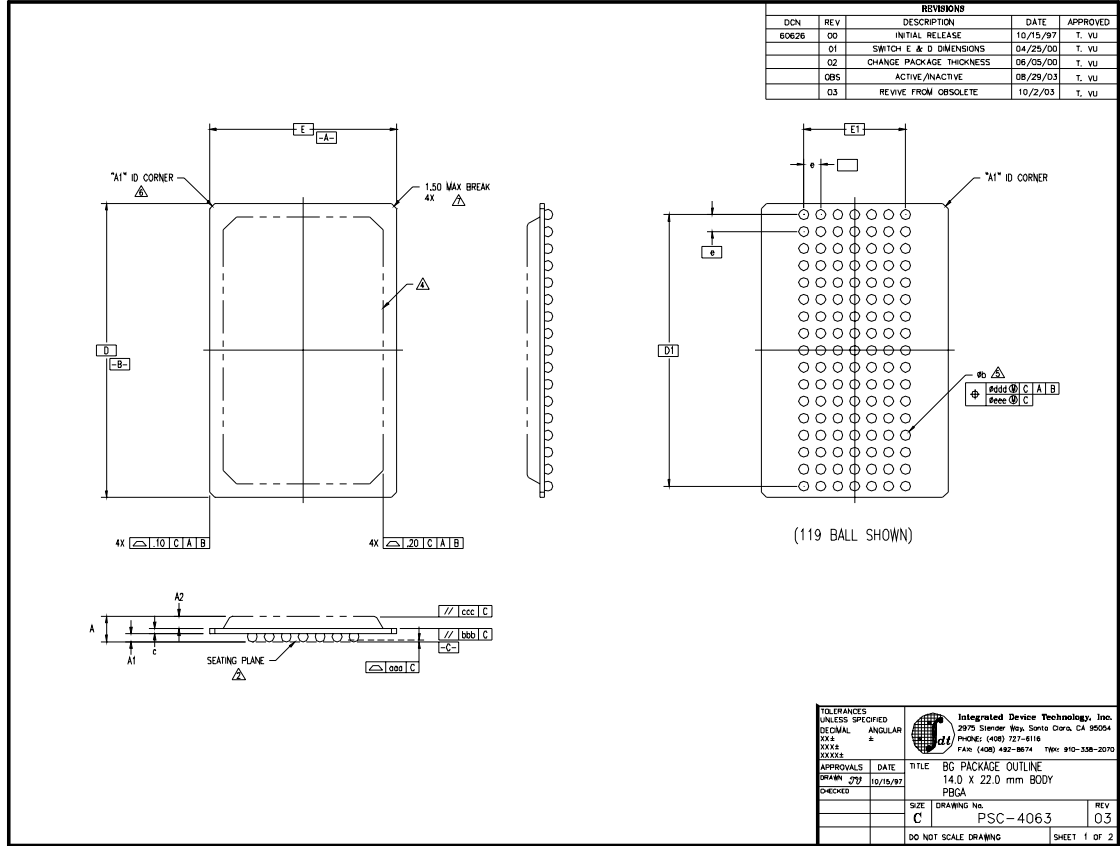


SYMBOL	JEDEC VARIATION			PINS
	MIN	NOM	MAX	
A	-	-	1.60	
A1	.05	.10	.16	
A2	1.35	1.40	1.45	
D	22.00 BSC			4
D1	20.00 BSC			5,2
E	16.00 BSC			4
E1	14.00 BSC			5,2
N	100			
ND	30			
NE	20			
e	65 BSC			
b	.22	.32	.38	7
b1	.22	.30	.33	
ccc	-	-	.10	
ddd	-	-	.13	

NOTES:

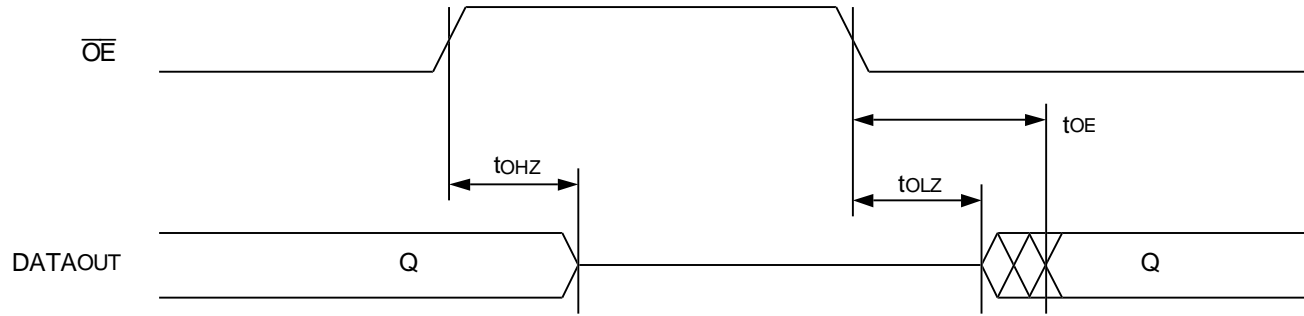
- 1 ALL DIMENSIONING AND TOLERANCING CONFORM TO ANSI Y14.5M-1982
- 2 TOP PACKAGE MAY BE SMALLER THAN BOTTOM PACKAGE BY .15 mm
- 3 DATUMS [A-B] AND [-D-] TO BE DETERMINED AT DATUM PLANE [-H-]
- 4 DIMENSIONS D AND E ARE TO BE DETERMINED AT SEATING PLANE [-C-]
- 5 DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD PROTRUSION, ALLOWABLE MOLD PROTRUSION IS .25 mm PER SIDE. D1 AND E1 ARE MAXIMUM BODY SIZE DIMENSIONS INCLUDING MOLD MISMATCH
- 6 DETAILS OF PIN 1 IDENTIFIER IS OPTIONAL, BUT MUST BE LOCATED WITHIN THE ZONE INDICATED
- 7 DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION, ALLOWABLE DAMBAR PROTRUSION IS .08 mm IN EXCESS OF THE b DIMENSION AT MAXIMUM MATERIAL CONDITION, DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT.
- 8 EXACT SHAPE OF EACH CORNER IS OPTIONAL
- 9 THESE DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .10 AND .25 mm FROM THE LEAD TIP
- 10 ALL DIMENSIONS ARE IN MILLIMETERS
- 11 THIS OUTLINE CONFORMS TO JEDEC PUBLICATION 95 REGISTRATION MO-136, VARIATION DJ AND BX

119 Ball Grid Array (BGA) Package Diagram Outline



SYMBOL	JEDEC VARIATION			NOTE
	AA			
	MIN	NOM	MAX	
A	-	2.15	2.36	
A1	.50	.60	.70	
A2	-	-	1.20	
D		22.00	BSC	
D1		20.32	BSC	
E		14.00	BSC	
E1		7.62	BSC	
MD		17	3	
ME		7	3	
N		119	3	
e		1.27	BSC	
b	.60	.75	.90	5
c	.51	.56	.61	
ooo	-	-	.15	
bbb	-	-	.25	
ccc	-	-	.35	
ddd	-	-	.30	
eee	-	-	.10	

Timing Waveform of \overline{OE} Operation⁽¹⁾

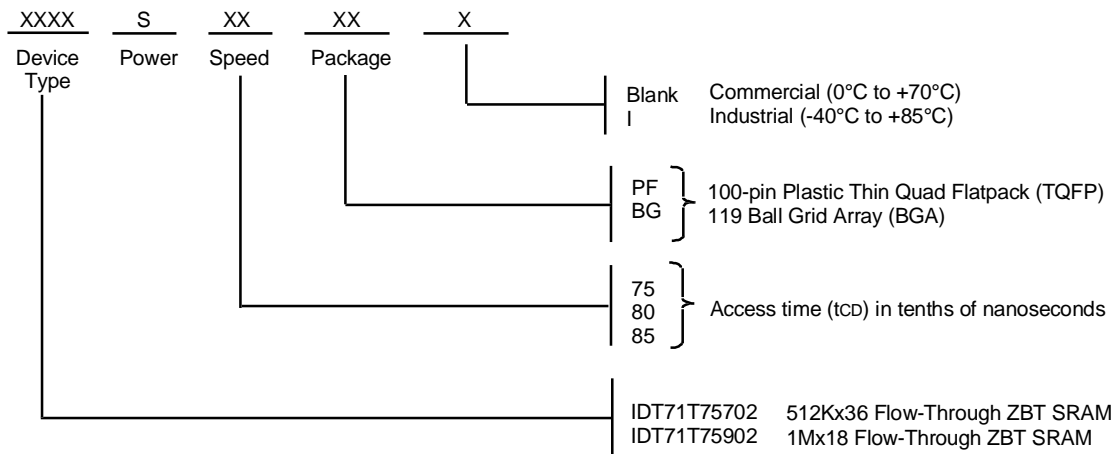


5319 drw 11

NOTE:

1. A read operation is assumed to be in progress.

Ordering Information



5319 drw 12

Datasheet Document History

Rev	Date	Pages	Description
0	05/25/00		Created Advance Information Datasheet
1	08/24/01	p. 1, 25	Removed reference of BQ165 package
		p. 8	Removed page of the 165 BGA pin configuration
		p. 24	Removed page of the 165 BGA package diagram outline
2	10/16/01	p. 7	Corrected 3.3V to 2.5V in Note 3
3	12/21/01	p. 5-7	Added clarification to JTAG pins, allow for NC. Added 36M address pin locations
4	05/29/02	p. 21	Corrected 100-pin TQFP package drawing
5	06/07/02	p. 1-4, 7, 14, 21, 22	Added complete JTAG functionality.
		p. 2, 14	Added notes for ZZ pin internal pulldown and ZZ leakage current.
		p. 14	Updated ISB3 power supply current from 40 to 60mA for all speeds.
6	11/19/02	p. 1-26	Changed datasheet from Advanced information to final release.
7	05/23/03	p. 5, 6, 14, 15, 25	Added I-temp to the datasheet.
		p. 6	Updated 165 BGA table.
8	02/29/04	p. 1	Updated logo with new design.
		p. 5, 6	Clarified ambient and case operating temperatures. Updated recommended operating temperature and supply voltage table and removed note 1.
		p. 7	Updated I/O pin number order for the 119 BGA.
9	02/20/09	p. 25	Removed "IDT" from orderable parts number
10	07/28/08: 05/13/15:		PDN SR-08-03R2 issued. See IDT.com for PDN specifics 71T75702 Datasheet changed to Obsolete Status

Notice

1. Descriptions of circuits, software and other related information in this document are provided only to illustrate the operation of semiconductor products and application examples. You are fully responsible for the incorporation or any other use of the circuits, software, and information in the design of your product or system. Renesas Electronics disclaims any and all liability for any losses and damages incurred by you or third parties arising from the use of these circuits, software, or information.
2. Renesas Electronics hereby expressly disclaims any warranties against and liability for infringement or any other claims involving patents, copyrights, or other intellectual property rights of third parties, by or arising from the use of Renesas Electronics products or technical information described in this document, including but not limited to, the product data, drawings, charts, programs, algorithms, and application examples.
3. No license, express, implied or otherwise, is granted hereby under any patents, copyrights or other intellectual property rights of Renesas Electronics or others.
4. You shall not alter, modify, copy, or reverse engineer any Renesas Electronics product, whether in whole or in part. Renesas Electronics disclaims any and all liability for any losses or damages incurred by you or third parties arising from such alteration, modification, copying or reverse engineering.
5. Renesas Electronics products are classified according to the following two quality grades: "Standard" and "High Quality". The intended applications for each Renesas Electronics product depends on the product's quality grade, as indicated below.
 - "Standard": Computers; office equipment; communications equipment; test and measurement equipment; audio and visual equipment; home electronic appliances; machine tools; personal electronic equipment; industrial robots; etc.
 - "High Quality": Transportation equipment (automobiles, trains, ships, etc.); traffic control (traffic lights); large-scale communication equipment; key financial terminal systems; safety control equipment; etc.Unless expressly designated as a high reliability product or a product for harsh environments in a Renesas Electronics data sheet or other Renesas Electronics document, Renesas Electronics products are not intended or authorized for use in products or systems that may pose a direct threat to human life or bodily injury (artificial life support devices or systems; surgical implantations; etc.), or may cause serious property damage (space system; undersea repeaters; nuclear power control systems; aircraft control systems; key plant systems; military equipment; etc.). Renesas Electronics disclaims any and all liability for any damages or losses incurred by you or any third parties arising from the use of any Renesas Electronics product that is inconsistent with any Renesas Electronics data sheet, user's manual or other Renesas Electronics document.
6. When using Renesas Electronics products, refer to the latest product information (data sheets, user's manuals, application notes, "General Notes for Handling and Using Semiconductor Devices" in the reliability handbook, etc.), and ensure that usage conditions are within the ranges specified by Renesas Electronics with respect to maximum ratings, operating power supply voltage range, heat dissipation characteristics, installation, etc. Renesas Electronics disclaims any and all liability for any malfunctions, failure or accident arising out of the use of Renesas Electronics products outside of such specified ranges.
7. Although Renesas Electronics endeavors to improve the quality and reliability of Renesas Electronics products, semiconductor products have specific characteristics, such as the occurrence of failure at a certain rate and malfunctions under certain use conditions. Unless designated as a high reliability product or a product for harsh environments in a Renesas Electronics data sheet or other Renesas Electronics document, Renesas Electronics products are not subject to radiation resistance design. You are responsible for implementing safety measures to guard against the possibility of bodily injury, injury or damage caused by fire, and/or danger to the public in the event of a failure or malfunction of Renesas Electronics products, such as safety design for hardware and software, including but not limited to redundancy, fire control and malfunction prevention, appropriate treatment for aging degradation or any other appropriate measures. Because the evaluation of microcomputer software alone is very difficult and impractical, you are responsible for evaluating the safety of the final products or systems manufactured by you.
8. Please contact a Renesas Electronics sales office for details as to environmental matters such as the environmental compatibility of each Renesas Electronics product. You are responsible for carefully and sufficiently investigating applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive, and using Renesas Electronics products in compliance with all these applicable laws and regulations. Renesas Electronics disclaims any and all liability for damages or losses occurring as a result of your noncompliance with applicable laws and regulations.
9. Renesas Electronics products and technologies shall not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any applicable domestic or foreign laws or regulations. You shall comply with any applicable export control laws and regulations promulgated and administered by the governments of any countries asserting jurisdiction over the parties or transactions.
10. It is the responsibility of the buyer or distributor of Renesas Electronics products, or any other party who distributes, disposes of, or otherwise sells or transfers the product to a third party, to notify such third party in advance of the contents and conditions set forth in this document.
11. This document shall not be reprinted, reproduced or duplicated in any form, in whole or in part, without prior written consent of Renesas Electronics.
12. Please contact a Renesas Electronics sales office if you have any questions regarding the information contained in this document or Renesas Electronics products.

(Note1) "Renesas Electronics" as used in this document means Renesas Electronics Corporation and also includes its directly or indirectly controlled subsidiaries.

(Note2) "Renesas Electronics product(s)" means any product developed or manufactured by or for Renesas Electronics.

(Rev.4.0-1 November 2017)

Corporate Headquarters

TOYOSU FORESIA, 3-2-24 Toyosu,
Koto-ku, Tokyo 135-0061, Japan
www.renesas.com

Contact Information

For further information on a product, technology, the most up-to-date version of a document, or your nearest sales office, please visit:
www.renesas.com/contact/

Trademarks

Renesas and the Renesas logo are trademarks of Renesas Electronics Corporation. All trademarks and registered trademarks are the property of their respective owners.